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**ACCELERATED LIFE TESTING EFFECT ON CMOS MICROCIRCUIT
CHARACTERISTICS,**

B. MAXIMOW

**RCA, SOLID STATE DIVISION
SOMERVILLE, NEW JERSEY**

DECEMBER 1976

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ACCELERATED LIFE TESTING EFFECTS ON CMOS MICROCIRCUIT CHARACTERISTICS

Phase I Report

May 1976 to December 1976

By

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Contract NAS-31905

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ABSTRACT

This report describes the work performed under NASA contract NAS8-31905 by the RCA Solid State Division, Somerville, N.J. facility and the integrated-circuits manufacturing facility in Findlay, Ohio. This report covers Phase I of the contract and the time period from May 1976 to December 1976.

In order for the results from Phase I (250°C) to be meaningful, data generated from Phase II (200°C) and Phase III (125°C) must be considered. This data, although preliminary, is included in this report. Subsequent reports will tie the data from all three phases of this contract together so that meaningful analyses and recommendations can be made.

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SECTION I INTRODUCTION

The need for a practical short-term test program, the results of which can be meaningfully interpreted to predict the long-term reliability of CMOS microcircuits, has been recognized. Many months if not years are required to run a life test under conditions reflecting actual applications and requirements of Class A devices. The impracticality of such a test led to the reliance by the industry on long-term reliability predictions based on interpolations of results gathered from accelerated life tests. It is essential to run long (thousands of hours) 125°C life tests to confirm experimentally the validity of such interpolations for CMOS devices. There is a definite possibility that accelerated tests cause the temperature thresholds of a device to be exceeded, thus triggering failure mechanisms unrelated to a device's operation within its specified ratings. The somewhat arbitrary limits established for the use of accelerated life tests must be either experimentally confirmed or revised in accordance with experimental data. The varying complexity of present day CMOS devices should be recognized as a factor in reliability predictions.

The purpose of this program is to determine the consistency of the CMOS microcircuit activation energy between the range of 125°C to 200°C and the range of 200°C to 250°C. Also, this program will determine the relationship of accelerated life-test failures to rated temperature operation and develop a test specification for accelerated life tests within the scope of the M38510 specifications.

The program encompasses three phases. Phase I is the 250°C accelerated life test, Phase II is the 200°C accelerated life test, and Phase III is the 125°C accelerated life test.

SECTION II
OBJECTIVE

The objective of Phase I of this program is:

1. To conduct an accelerated life test of sufficient duration to generate a minimum of 50% cumulative failures in each lot of devices. This data coupled with data generated in Phase II and Phase III should provide a basis for determining the consistency of the activation energy among the three temperatures (250°C, 200°C, and 125°C).
2. To provide a basis for recommendations of conditions and limits to be used as part of a microcircuits qualification procedure.
3. To determine whether any thresholds are exceeded during the high temperature testing, which could trigger failure mechanisms unique to that temperature.
4. To determine the usefulness of the 250°C temperature life test as a predictor of long-term reliability.

SECTION III DEVICE SELECTION

The choice of microcircuit devices for this program was made according to the following criteria:

1. High-reliability Class A devices.
2. Varying degree of complexity representing the product line.
3. Availability.

The following microcircuit types were chosen for this program:

<u>MIL DESIGNATIONS</u>	<u>GENERIC NAMES</u>	<u>FUNCTION</u>
M38510/05001ADX	CD4011A	Two-input quadruple logic gate
M38510/05101ADX	CD4013A	"D"-type flip-flop
M38510/05605ADX	CD4024A	Seven-stage binary counter.

The devices are in flat packs with weldable leads. Solder-dipped leads could not be used at temperatures above the solder melting point. These devices were tested to the individual M38510/50 specifications. Table III of these specifications is attached to this report as Table I (CD4011A), Table II (CD4013A), and Table III (CD4024A). The table specifies the electrical parameters' test conditions and limits for the group A testing for individual microcircuits. Subgroups 1,2,3,7, and 8 were performed at each measurement point throughout the test program and are the basis for the consequent data analysis.

TABLE III Group A inspection for device type D1
Terminal conditions (pins not designated are open)

Symbol	MIL-STD-883 Method	Case	Test limits														Unit						
			Subgroup 1 $T_A = 25^\circ C$		Subgroup 2 $T_A = 125^\circ C$		Subgroup 3 $T_A = -55^\circ C$																
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max							
V_{IC} (POS)		1 2 3 4 5 6 7 8	1 mA	1 mA			1 mA	1 mA	GND						SND	1A 1B 2B 2A 3A 3B 4B 4A	1.5				Vdc		
V_{IC} (NEG)		9 10 11 12 13 14 15 16	-1 mA	-1 mA			-1 mA	-1 mA	GND						GND	1A 1B 2B 2A 3A 3B 4B 4A	-6.0				Vdc		
I_{SS}	3005	17 18 19	GND 15.0 V 15.0 V	15.0 V GND 15.0 V			15.0 V GND 15.0 V	15.0 V GND 15.0 V	GND	GND	15.0 V GND 15.0 V	15.0 V GND 15.0 V			15.0 V GND 15.0 V	15.0 V GND 15.0 V	V _{SS}	-25.0		-750.0		nA	
V_{OHT}	3006	20 21 22 23 24 25 26 27	V_{IL1} 5.0 V GND	5.0 V V _{IL1} GND	I_{OHT}	I_{OH1}	V_{IL1} 5.0 V GND	V_{IL1} 5.0 V GND	GND	GND	V_{IL1} 5.0 V GND	V_{IL1} 5.0 V GND			GND	GND 5.0 V	1Y 1Y 2Y 2Y 3Y 3Y 4Y 4Y	4.2		4.2		Vdc	
V_{OHz}	3006	28 29 30 31 32 33 34 35	V_{IL1} 5.0 V GND	5.0 V V_{IL1} GND			GND V_{IL1} 5.0 V GND	GND V_{IL1} 5.0 V GND	GND	GND	GND V_{IL1} 5.0 V GND	GND V_{IL1} 5.0 V GND			GND	GND 5.0 V	1Y 1Y 2Y 2Y 3Y 3Y 4Y 4Y	4.95		4.95		4.95	Vdc
V_{OH3}	3006	36 37 38 39	V_{IL2} 12.5 V GND	12.5 V V_{IL2} GND			GND V_{IL2} 12.5 V GND	GND V_{IL2} 12.5 V GND	GND	GND	GND V_{IL2} 12.5 V GND	GND V_{IL2} 12.5 V GND			GND	GND 12.5 V	1Y 1Y 2Y 2Y	11.25		11.25		11.25	Vdc

TABLE I - Device: CD4011A, M38510/05001ADX, Group A inspection.

TABLE III Group A inspection for device type 01 (cont.)
Terminal conditions (pins not designated are open)

Symbol	MIL-STD-883 Method	Case	Test limits														Unit	
			Subgroup 1 $T_A = 25^\circ C$		Subgroup 2 $T_A = 125^\circ C$		Subgroup 3 $T_A = -55^\circ C$											
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
V_{O13}	3006	A11	1A	2	3	4	5	6	7	8	9	10	11	12	13	14		
		Symbol	40	GND	GND				GND	GND								
		Test No	41															
			42															
			43															
V_{OL1}	3007	1A	44	V_{IH1} GND	V_{IH1} GND	I_{OL1}	E_{OL1}	GND	GND	GND	GND	I_{OL1}	GND	V_{IL2} 12.5 V	V_{IL2} 12.5 V	3Y	11.25	
			45													3Y		
			46													4Y		
			47													4Y		
V_{OL2}	3007	2A	48	V_{IH1} GND	V_{IH1} GND			GND	GND	GND	GND			V_{IL2} 12.5 V	V_{IL2} 12.5 V	1Y	0.5	
			49													2Y		
			50													3Y		
			51													4Y		
V_{CL3}	3007	3A	52	V_{IH2} GND	V_{IH2} GND			GND	GND	GND	GND			V_{IL2} 12.5 V	V_{IL2} 12.5 V	1Y	1.25	
			53													2Y		
			54													3Y		
			55													4Y		
I_{IH1}	3010	4A	56	15.0 V	15.0 V			15.0 V	15.0 V	GND	15.0 V	15.0 V	15.0 V	15.0 V	15.0 V	A11 together	8.0	nA
I_{IH2}	3010	5A	57	15.0 V GND	15.0 V GND			GND	GND	GND	GND			V_{IL2} 12.5 V	V_{IL2} 12.5 V	1A	45.0	
			58													1B		
			59													2B		
			60													2A		
			61													3A		
			62													3B		
			63													4B		
			64													4A		
I_{IL1}	3009	6A	65	GND	GND			GND	GND	GND	GND			V_{IL2} 12.5 V	V_{IL2} 12.5 V	A11 together	-8.0	nA
I_{IL2}	3009	6B	66	GND	GND			GND	GND	GND	GND			V_{IL2} 12.5 V	V_{IL2} 12.5 V	1A	-45.0	
			67													1B		
			68													2B		
			69													2A		
			70													3A		
			71													3B		
			72													4B		
			73													4A		

TABLE I - Device. CD4011A, M38510/05001ADX, Group A inspection (Continued).

MIL-STD-883C
M38510/05001ADX

TABLE III Group A inspection for device type 01 (cont.)
Terminal conditions (pins not designated are open)

Symbol	MIL-STD-883 Method	Case															Measured terminal	Test limits				Unit					
			1	2	3	4	5	6	7	8	9	10	11	12	13	14		Subgroup 4 $T_A = 25^\circ C$									
		Symbol	1A	1B	1Y	2Y	2B	2A	V_{SS}	3A	3B	3Y	4Y	4B	4A	V_{DD}		Min	Max								
		Test No																									
C_1	3012	74 75 76 77 78 79 80 81	F					F	F	GND							1A 1B 2B 2A 3A 3B 4B 4A	12.0				pF					
t_{PHL}	3003 Fig 7	82 83 94 85 86 87 88 89	IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	OUT	OUT	5.0 V 5.0 V IN 5.0 V	5.0 V	GND	5.0 V IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	5.0 V IN 5.0 V	5.0 V IN	5.0 V IN	5.0 V IN	1A to 1Y 1B to 1Y 2A to 2Y 2B to 2Y 3A to 3Y 3B to 3Y 4A to 4Y 4B to 4Y	20	175	30	250	15	140	ns
t_{PLH}	3003 Fig 7	90 91 92 93 94 95 96 97	IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	OUT	OUT	5.0 V 5.0 V IN 5.0 V	5.0 V	GND	5.0 V IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	5.0 V IN 5.0 V	5.0 V IN	5.0 V IN	5.0 V IN	1A to 1Y 1B to 1Y 2A to 2Y 2B to 2Y 3A to 3Y 3B to 3Y 4A to 4Y 4B to 4Y	20	150	30	215	15	120	ns
t_{THL}	3004 Fig 7	98 99 100 101 102 103 104 105	IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	OUT	OUT	5.0 V 5.0 V IN 5.0 V	5.0 V	GND	5.0 V IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	5.0 V IN 5.0 V	5.0 V IN	5.0 V IN	5.0 V IN	1Y 1Y 2Y 2Y 3Y 3Y 4Y 4Y	30	250	45	360	25	200	ns
t_{TLH}	3004 Fig 7	106 107 108 109 110 111 112 113	IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	OUT	OUT	5.0 V 5.0 V IN 5.0 V	5.0 V	GND	5.0 V IN 5.0 V	5.0 V IN 5.0 V	OUT	OUT	5.0 V IN 5.0 V	5.0 V IN	5.0 V IN	5.0 V IN	1Y 1Y 2Y 2Y 3Y 3Y 4Y 4Y	40	300	60	430	30	240	ns

TABLE I - Device: CD4011A, M38510/05001ADX, Group A inspection (Continued).

TABLE III Group A inspection for device type 01

Symbol	MIL-STD-883 method	Cases C, D	Terminal conditions and limits														Measured terminal	Test limits						Units		
			Symbol		Q ₁	Q̄ ₁	CLK ₁	RS ₁	D ₁	SET ₁	V _{SS}	SET ₂	D ₂	RS ₂	CLK ₂	Q ₂	Q̄ ₂	V _{DD}	Subgroup 1 T _A = 25°C		Subgroup 2 T _A = 125°C					
			Test No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	Min	Max	Min	Max	Min	Max			
V _{IC(pos)}			1							1 mA							GND		Set 1 RS ₁ D ₁ CLK ₁ SET ₂ RS ₂ D ₂ CLK ₂	1	5				V _{dc}	
			2							1 mA																
			3																							
			4																							
			5																							
			6																							
			7																							
			8																							
V _{IC(neg)}			9																Set 1 RS ₁ D ₁ CLK ₁ SET ₂ RS ₂ D ₂ CLK ₂	-3						
			10																							
			11																							
			12																							
			13																							
			14																							
			15																							
			16																							
I _{SS} See note B	3005		17					15 V	GND	GND	GND	GND	GND	GND	GND	GND	GND	15 V	None		-25	-25			μA	
			18					15 V																		
			19					15 V																		
			20					15 V																		
			21					15 V																		
			22					15 V																		
			23					15 V																		
			24					15 V																		
			25					15 V																		
			26					15 V																		
			27					15 V																		
			28					15 V																		
			29					15 V																		
			30					15 V																		
			31					15 V																		
			32					15 V																		
			33					15 V																		
			34					15 V																		
			35					15 V																		
			36					15 V																		
			37					15 V																		
			38					15 V																		

TABLE II – Device: CD4013A, M38510/05101ADX, Group A inspection.

TABLE II - Device: CD4013A, M383510/05101ADX, Group A inspection. (Continued)

Symbol	MIL-STD-883 method	Cases C, D	Terminal conditions and limits														Measured terminal	Test limits						Units			
			Symbol		Q ₁	Q̄ ₁	CLK ₁	RS ₁	D ₁	SET ₁	V _{SS}	SET ₂	D ₂	RS ₂	CLK ₂	Q ₂	V _{DD}	Subgroup 1 TA = 25°C	Subgroup 2 TA = 125°C	Subgroup 3 TA = -55°C	Min	Max	Min	Max	Min	Max	
			Test No		1	2	3	4	5	6	7	8	9	10	11	12	13	14	Q ₁	Q̄ ₁	Q ₂	Q̄ ₂	Q ₁	Q̄ ₁	Q ₂	Q̄ ₂	
V _{OH1}	3006		39 40 41 42	I _{OH}	I _{OH}	GND	V _{IL1} V _{IH1}	GND	V _{IH1}	GND	GND	GND	GND	GND	GND	5 0 V	Q ₁ Q̄ ₁	4 5	Q ₁ Q̄ ₁	4 5		4 5				Vdc	
V _{OH2}			43 44 45 46				V _{IL1} V _{IH1}		V _{IH1}	GND	GND	GND	GND	GND	GND		I _{OH}		Q ₁ Q̄ ₁	4 95	Q ₁ Q̄ ₁	4 95		4 95			
V _{OH3}			47 48 49 50				V _{IL2} V _{IH2}	GND	V _{IL2}	GND	GND	V _{IL2} V _{IH2}	GND	GND	GND			12 5 V	Q ₁ Q̄ ₁	11 25	Q ₁ Q̄ ₁	11 25		11 25			
V _{OL1}	3007		51 52 53 54	I _{OL}	I _{OL}		V _{IL1} V _{IL1}	GND	V _{IL1}	V _{IL1} V _{IH1}	GND	GND	V _{IL1} V _{IL1}	GND	GND	5 0 V	I _{OL}	I _{OL}	Q ₁ Q̄ ₁	0 5	Q ₁ Q̄ ₁	0 5		0 5			
V _{OL2}			55 56 57 58				V _{IL1} V _{IL1}	GND	V _{IL1}	V _{IL1} V _{IH1}	GND	GND	V _{IL1} V _{IL1}	GND	GND		I _{OL}		Q ₁ Q̄ ₁	0 5	Q ₁ Q̄ ₁	0 5		0 5			
V _{OL3}			59 60 61 62				V _{IL2} V _{IL2}	GND	V _{IL2}	V _{IL2} V _{IH2}	GND	GND	V _{IL2} V _{IL2}	GND	GND	12 5 V	I _{OL}		Q ₁ Q̄ ₁	1 25	Q ₁ Q̄ ₁	1 25		1 25			
V _{OH4}			63		I	GND	V _{IL1}	I			GND			GND			5 0 V		Q ₁	4 95	Q ₁	4 95		4 95			
V _{OL4}			64		I		V _{IL1}	I		GND									Q ₁		Q ₁		0 05	0 05		0 05	
V _{OH4}			65			GND		GND	GND		I	V _{IL1}		I					Q ₂	4 95	Q ₂	4 95		4 95			
V _{OL4}			66 67			GND	I	GND	GND		I	V _{IL1} GND		I	GND				Q ₂ Q ₁		Q ₂ Q ₁		0 05	0 05		0 05	0 05
V _{OH4}			68		I		V _{IH1}	I		GND	GND		GND	GND		GND			Q ₁	4 95	Q ₁	4 95		4 95			
V _{OL4}			69			GND		GND	GND		I	V _{IH1}		I					Q ₂		Q ₂		0 05	0 05		0 05	
V _{OH4}			70			GND		GND	GND		I	V _{IH1}		I					Q ₂	4 95	Q ₂	4 95		4 95			
V _{ICL1} V _{ICL1}			71 72		J		J	J		GND	GND		GND	GND		GND			CLK ₁ , J CLK ₁ , J	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	
V _{ICL2} V _{ICL2}			73 74			GND	GND		GND	GND		J	J	J	J				CLK ₂ , J CLK ₂ , J	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	V _{IL1}	

TABLE III Group A Inspection for device type 01 - Continued

Symbol	MIL-STD-883 method	Cases C D	Terminal conditions and limits														Measured terminal	Test limits						Units		
			Symbol		Q1	Q̄1	CLK ₁	RS ₁	D ₁	SFT ₁	V _{SS}	SET ₂	D ₂	RS ₂	CLK ₂	Q̄2	Q ₂	V _{DD}	Subgroup 1 T _A = 25°C		Subgroup 2 T _A = 125°C		Subgroup 3 T _A = -55°C			
			Test No		1	2	3	4	5	6	7	8	9	10	11	12	13	14	Min	Max	Min	Max	Min	Max		
I _{HW1} See note K	3010	75					15 V	15 V	15 V	15 V	GND	15 V	15 V	15 V	15 V			15 V		A11 inputs together	8				nA	
I _{HW2}		76 77 78 79 80 81 82 83																	CLK ₁ RS ₁ D ₁ SET ₁ SET ₂ D ₂ RS ₂ CLK ₂	1 0		45				
I _{HL1} See note K	3009	84					GND	GND	GND	GND		GND	GND	GND	GND				All inputs together	-8 0						
I _{HL2}		85 86 87 88 89 90 91 92																CLK ₁ RS ₁ D ₁ SET ₁ SET ₂ D ₂ RS ₂ CLK ₂	-1 0		-45					
C ₁	3012	93 94 95 96 97 98 99 100				L	L	L	L	GND	L	L	L	L	GND		Subgroup 4 T _A = 25°C	12					pF			

TABLE II - Device. GD4013A, M38510/05101ADY, Group A inspection. (Continued)

TABLE II - Device. CD4013A, M38510/05101ADX, Group A inspection. (Continued)

TABLE III Group A inspection for device type 01 -Continued

MIL-M-38510/51E

TABLE II - Device: CD4013A, M38510/05101ADX, Group A inspection. (Continued)

Symbol	MIL-STD-883 method	Cases C D		Terminal conditions and limits												Measured terminal	Test limits						Units			
		Symbol	Q1	Q̄1	CLK1	RS1	D1	SET1	VSS	SET2	D2	RS2	CLK2	Q2	Q̄2	VDD	Subgroup 9 TA = 25°C	Subgroup 10 TA = 125°C	Subgroup 11 TA = -55°C							
		Test No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	Min	Max	Min	Max	Min	Max				
tPLH R or S ↓	3003 (Fig 12)	130	OUT					IN	GND							5.0 V	SET1 to Q1 RS1 to Q1 SET2 to Q2 RS2 to Q2	100	420	100	630	70	420	ns		
		131		OUT*		IN																				
		132																								
		133																								
tTHL	3004 (Fig 11)	134 135 136 137	OUT	OUT	IN	IN											IN IN	Q1 Q1 G1 G2 Q1 Q1 G1 G2	30	300	40	450	25	300		
tTLH	3004 (Fig 11)	138 139 140 141	OUT	OUT	IN	IN											IN IN	OUT OUT		350	525		350			
tCL (max) See note O	3004 (Fig 11)	142 143	OUT		IN												IN	OUT		0.67	0.67	1.0	1.0	0.67	μs	
tTLHCL (max) See note P	3004 (Fig 11)	144 145	OUT		IN												CLK1 CLK2		15		15		10		μs	
tP See note Q	(Fig 11)	146 147	OUT		IN												IN	OUT		CLK1	300	450		300	ns	
tSHL tSHL	(Fig 13)	148 149			IN	IN											IN	IN		D1 to CLK1 D2 to CLK2	150	225		150		
tSLH tSLH		150 151			IN	IN											IN	IN		D1 to CLK1 D2 to CLK2						
tHHL tHHL	(Fig 14)	152 153			IN	IN											IN	IN		D1 to CLK1 D2 to CLK2	300	450		300		
tHLH tHLH		154 155			IN	IN											IN	IN		D1 to CLK1 D2 to CLK2						

NOTES

- A Pins not designated may be "high" level logic, "low" level logic or open
- B Test numbers 17 thru 38 shall be run in sequence
- C $I_{OH} = -0.25 \text{ mA}$ at 25°C , -0.175 mA at 125°C , -0.31 mA at -55°C
- D $V_{IH1} = 3.8 \text{ V}$ at 25°C , 3.6 V at 125°C , 3.95 V at -55°C
- E $V_{IH2} = 9.5 \text{ V}$ at 25°C , 9.25 V at 125°C , 9.75 V at -55°C
- F $I_{OL} = 0.5 \text{ mA}$ at 25°C , 0.35 mA at 125°C , 0.65 mA at -55°C
- G $V_{IL1} = 1.1 \text{ V}$ at 25°C , 0.8 V at 125°C , 1.35 V at -55°C
- H $V_{IL2} = 2.8 \text{ V}$ at 25°C , 2.55 V at 125°C , 3.0 V at -55°C
- I For input conditions see Figure 9
- J For input voltage conditions see Figure 10

K The device manufacturer may, at his option, measure I_{IL} and I_{IH} at 25°C for each individual input or measure all inputs together

L See 4.4.1(c)

M Test numbers 101 thru 117 shall be run in sequence and the functional tests shall be performed with V_{IH} and $V_{DD} \leq 5.0 \text{ V}$ and $\geq 15.0 \text{ V}$

N L = 0.5 V maximum and H = 4.5 V minimum

O The maximum clock frequency (f_{CL}) requirement is considered met if proper output state changes occur with the pulse repetition period set to that given in the limits column

P Pulse repetition period = 100 μsec, 50 percent duty cycle. The maximum clock transition time (t_{TLHCL}) requirement is considered met if proper output state changes occur with the rise time set to that given in the limits column

Q The minimum clock pulse width (t_p) requirement is considered met if proper output state changes occur with the pulse width set to that given in the limits column

TABLE III Group A inspection for device type 05

Symbol	MIL-STD-883 method	Case C D	Terminal conditions (pins not designated are open)														Test limits						Units			
			1	2	3	4	5	6	7	8	9	10	11	12	13	14	Meas terminal	Subgroup 1 T _A = 25°C	Subgroup 2 T _A = 125°C	Subgroup 3 T _A = -55°C	Min	Max	Min	Max	Min	Max
I _{OH} I _{OL}	3010 3010	1 2	15 V GND	GND 15 V					GND							15 V	1 2		1 0		10		1 0	nAdc		
I _{VL} I _{IL}	3009 3009	3 4	GND GND	GND GND		-											1 2									
V _{OL2} V _{OH2} V _{OH1} V _{OL1}	3007 3006 3006 3007	5 6 7 8	A A B B	A A B B			C	D	C	D			C	D	C	5 0 V	A A B B	14 99 4 20 4 20 500	14 95 4 20 500	10 50 500		10 mVdc Vdc Vdc mVdc				
V _{ICL}		9	E	E													E		3 50		3 25		3 65	Vdc		
V _{IR}		10	F	F													F	1 50		1 25		1 75		Vdc		
I _{SS} I _{SS}	3005 3005	11 12	H 15 V	H 15 V												15 V	7 7		500		5000		500	nAdc nAdc		
C _i C _i	3012 3012	13 14	L	L					GND GND							GND GND	1 2	7 0 7 0						pF pF		
t _{PHL1}	3003	15 16 17 18 19 20 21	J	GND	G	G	G	G	GND			G	G	G	5 0 V	12 11 9 6 5 4 3	0 44 0 88 1 32 1 76 2 20 2 64 3 10	0 56 1 12 1 68 2 24 2 80 3 36 4 00	0 33 0 76 0 49 1 37 1 65 1 98 2 31		ps					
t _{PLH}		22 23 24 25 26 27 28														12 11 9 6 5 4 3	0 44 0 88 1 32 1 76 2 20 2 64 3 10	0 56 1 12 1 68 2 24 2 80 3 36 4 00	0 33 0 60 0 99 1 32 1 65 1 98 2 31							
t _{THL} t _{TLD}	3004 3004	29 30	V	V												J J	430 430	550 550	325 325	ns ns						
t _{RHL2}	3003	31	K	K	↓	↓	↓	↓	V	V	V	V	V	V	V	K	0 90	1 16	0 68	μs						
Subgroup 7 Verify truth table, figure 3 @ VDD ≤ 5 0 Vdc and ≥ 15 0 Vdc J _{OL} = V _{SS} + 0 ns Vdc V _{OH} = V _{DD} - 0 50 Vdc T _A = 25°C																										
Subgroup 8 Same test, terminal conditions and limits as subgroup 7 except T _A = 125°C and -55°C																										

NOTES

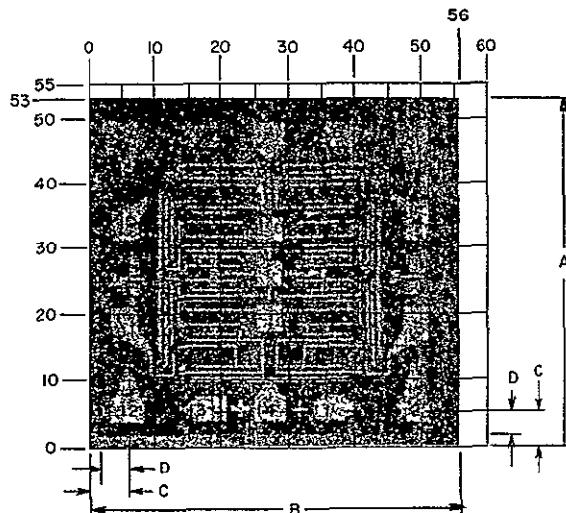
- A Each output shall be measured using the timing diagram of figure 26
- B Each output shall be measured using the timing diagram of figure 27
- C I_{OH} 15 μAdc @ 25°C -105 μAdc @ 125°C 185 μAdc @ -55°C
- D I_{OL} = 250 μAdc @ 25°C, 175 μAdc @ 125°C 310 μAdc @ -55°C
- E See figure 28 timing diagram
- F See figure 29 timing diagram
- G Load condition: C_L = 50 pF R_L = 200 kΩ
- H Check less than a half state (e.g. 2⁸⁻¹ and 2⁶) from figure 26, See figure 41 for test circuit and measurement points
- I See figure 2 for test circuit and measurement points

TABLE III - Device CD4024A, M38510/05605ADX, Group A inspection.

Further detailed description of these microcircuits is given in Figs. 1 through 7. Photographs of chips with dimensions grid, magnified photographs with detail visibility, logic diagrams, and circuit diagrams in these figures provide a basis for comparison of the chip sizes and complexities of the microcircuits involved.

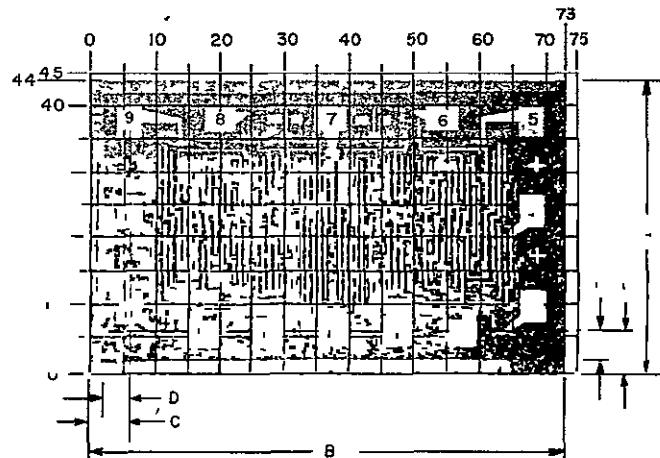
The table below summarizes these factors.

Type	<u>Si Area</u>	<u>No. of active elements</u>	<u>Number of inputs</u>	<u>Number of outputs</u>
CD4011A	1.9 mm ²	13	8	4
CD4013A	2.1 mm ²	64	8	4
CD4024A	4.2 mm ²	134	2	7



CD4011AH

92CS-22078

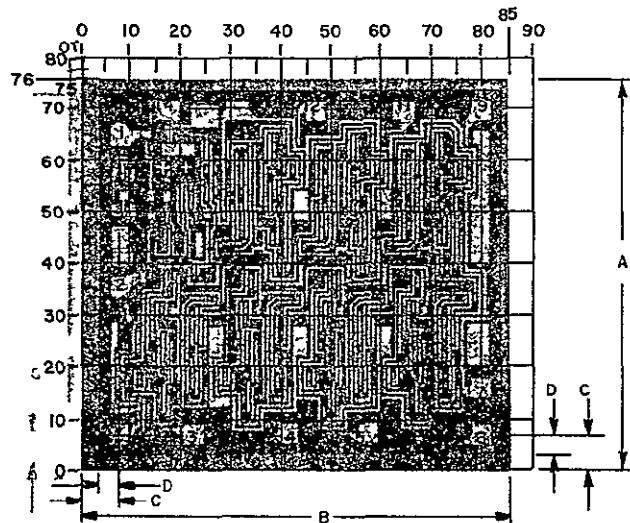


CD4013AH

92CS-22080

Grid Graduations Are In Mils (10^{-3} Inch)

TYPE	A*		B*		C		D		CHIP THICKNESS	
	Mils	Millimeters	Mils	Millimeters	Mils	Millimeters	Mils	Millimeters	Mils	Millimeters
CD4011AH	50 - 58	1.270 - 1.473	53 - 61	1.347 - 1.549	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.228
CD4012AH	50 - 58	1.270 - 1.473	53 - 61	1.347 - 1.549	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.228
CD4013AH	41 - 49	1.042 - 1.244	70 - 78	1.778 - 1.981	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.228
CD4014AH	79 - 87	2.007 - 2.209	81 - 89	2.058 - 2.260	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.228



CD4024AH

92CS-22090

Grid Graduations Are In Mils (10^{-3} Inch)

TYPE	A*		B*		C		D		CHIP THICKNESS	
	Mils	Millimeters	Mils	Millimeters	Mils	Millimeters	Mils	Millimeters	Mils	Millimeters
CD4023AH	53 - 61	1.347 - 1.549	53 - 61	1.347 - 1.549	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.288
CD4024AH	73 - 81	1.855 - 2.057	82 - 90	2.083 - 2.286	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.288
CD4025AH	49 - 57	1.245 - 1.447	51 - 59	1.297 - 1.498	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.228
CD4026AH	89 - 97	2.261 - 2.463	89 - 97	2.261 - 2.463	4 - 10	0.102 - 0.254	3.3 - 4.3	0.084 - 0.109	5 - 9	0.127 - 0.228

* The photographs and dimensions of each COS/MOS chip represent a chip when it is part of the wafer. When the wafer is cut into chips, the

cleavage angles are 57° instead of 90° with respect to the face of the chip. Therefore the isolated chip is actually 7 mils (0.17 mm) larger in both the A and B dimensions.

Fig. 1 - Dimensions of microcircuit chips.

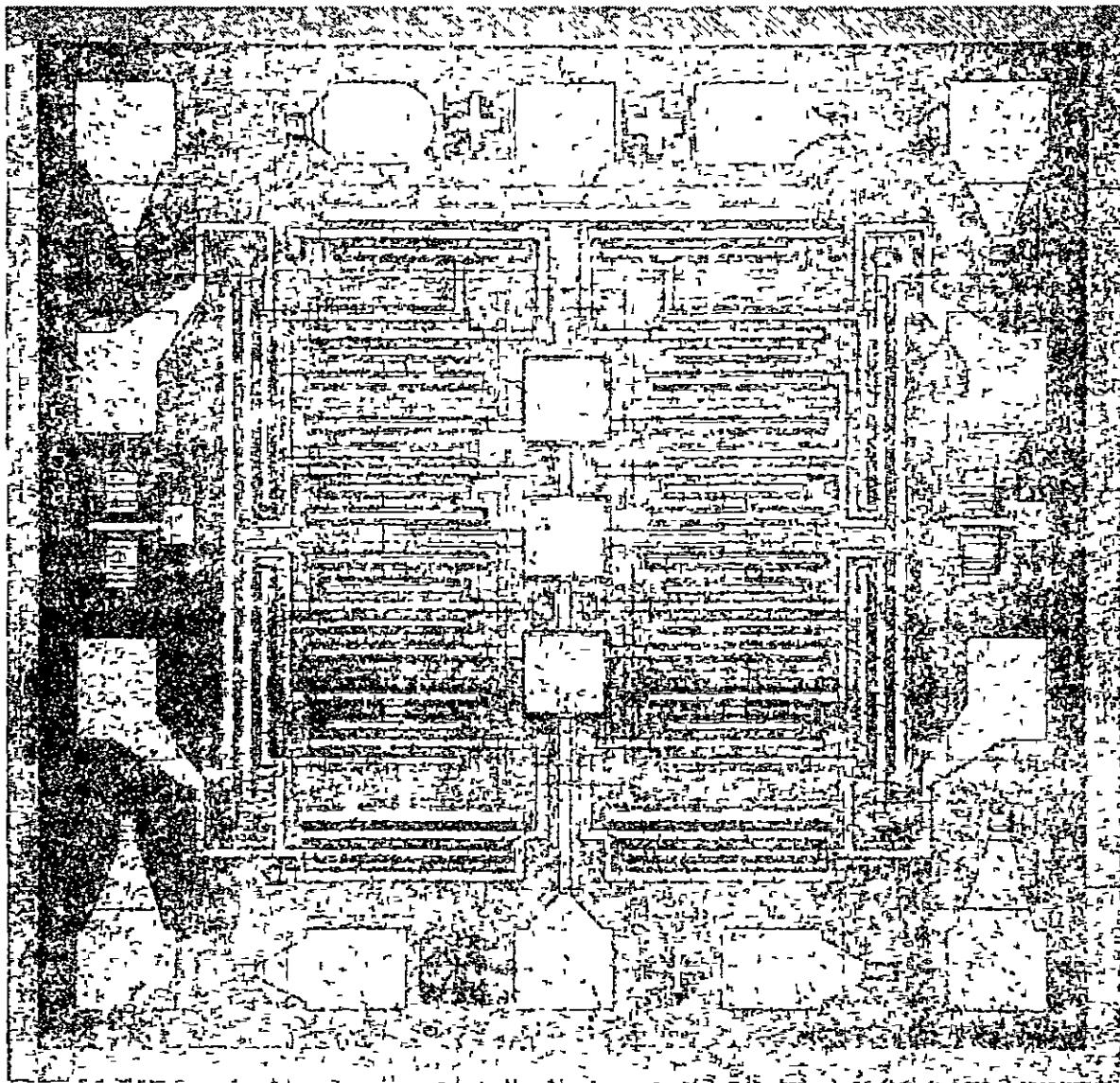


Fig. 2 - CD4011A microcircuit.

REPRODUCIBILITY OF THE
ORIGINAL PAGE IS POOR

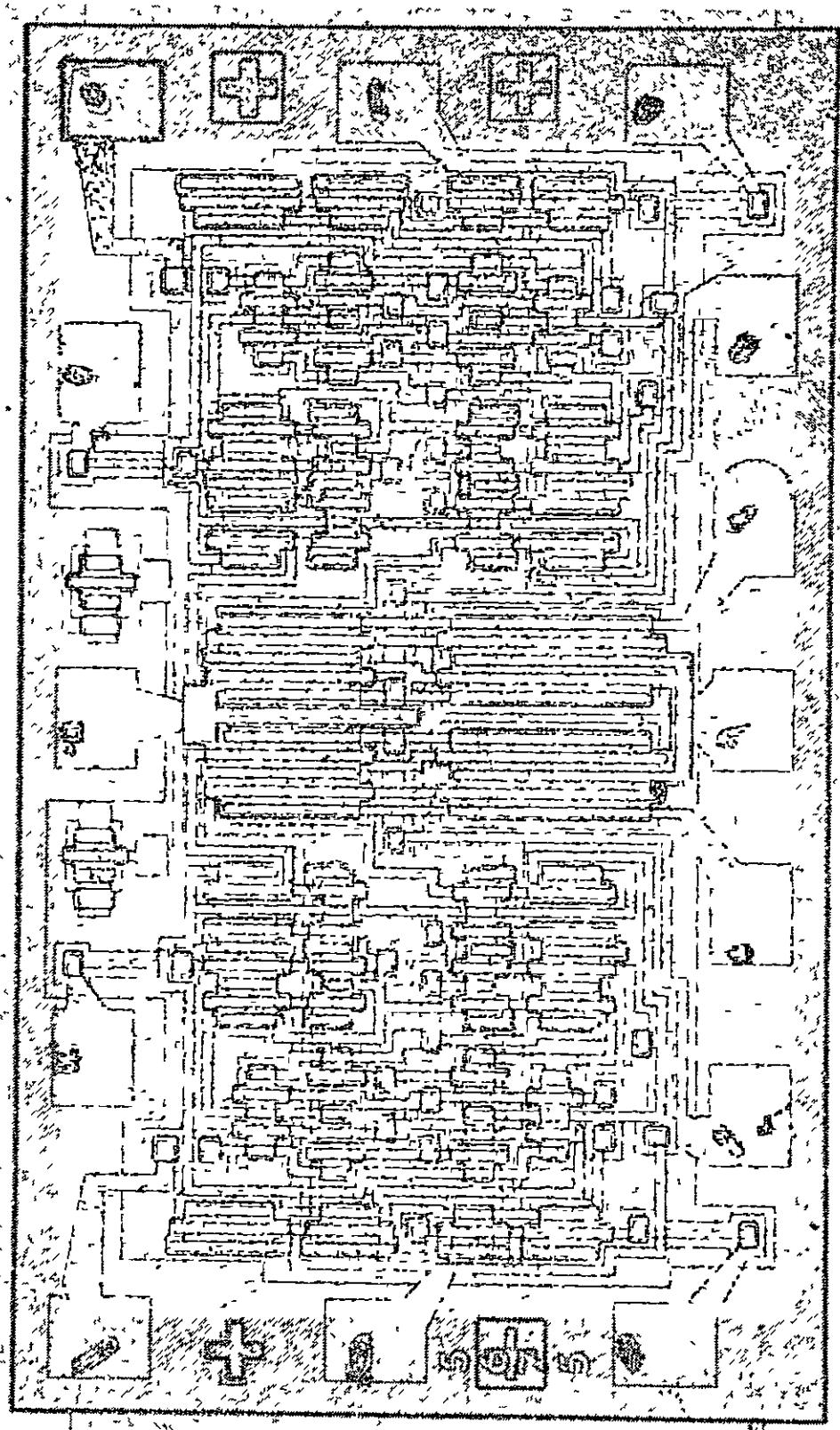


Fig. 3 - CD4013A microcircuit.

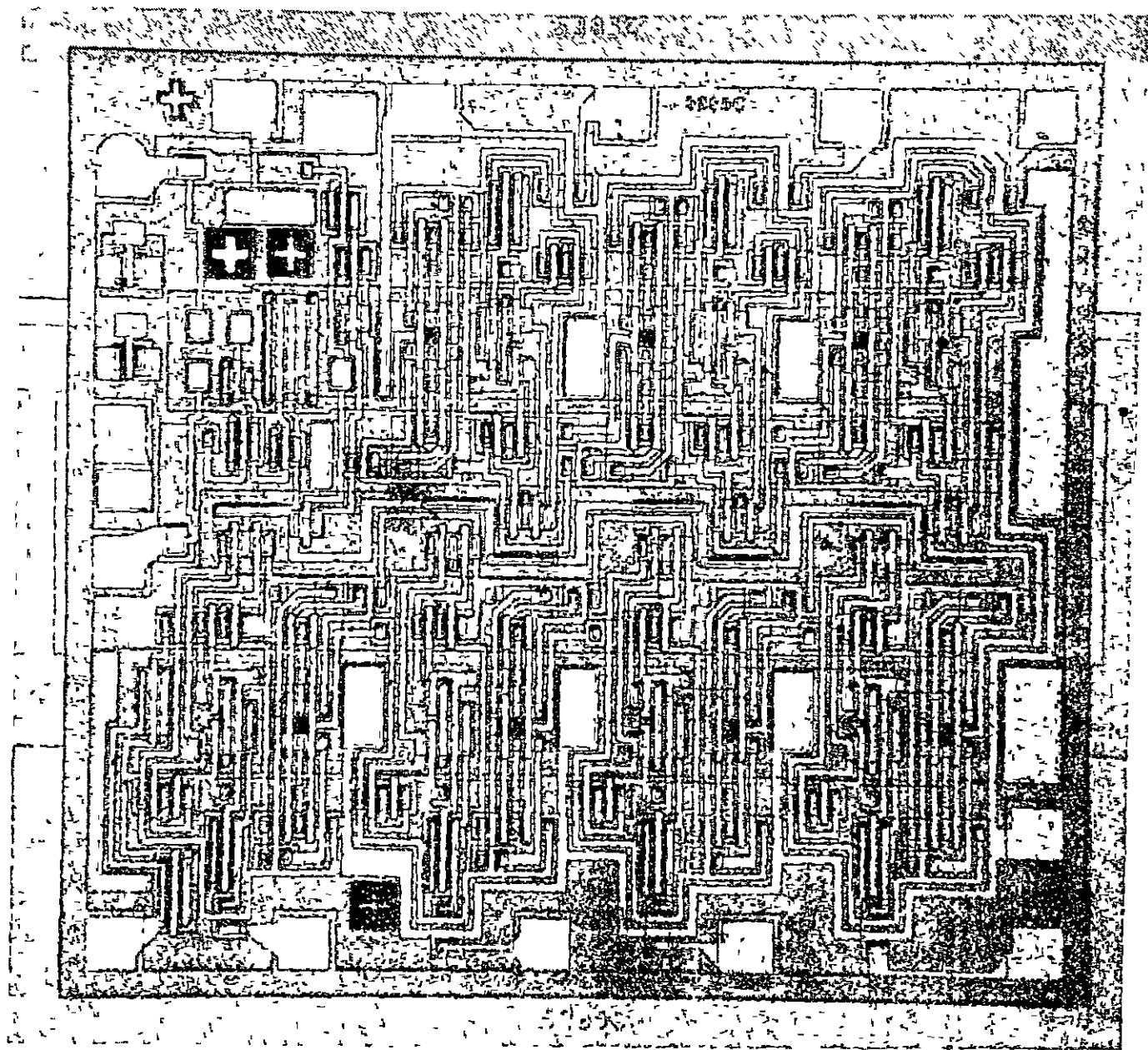


Fig. 4 - CD4024A microcircuit.

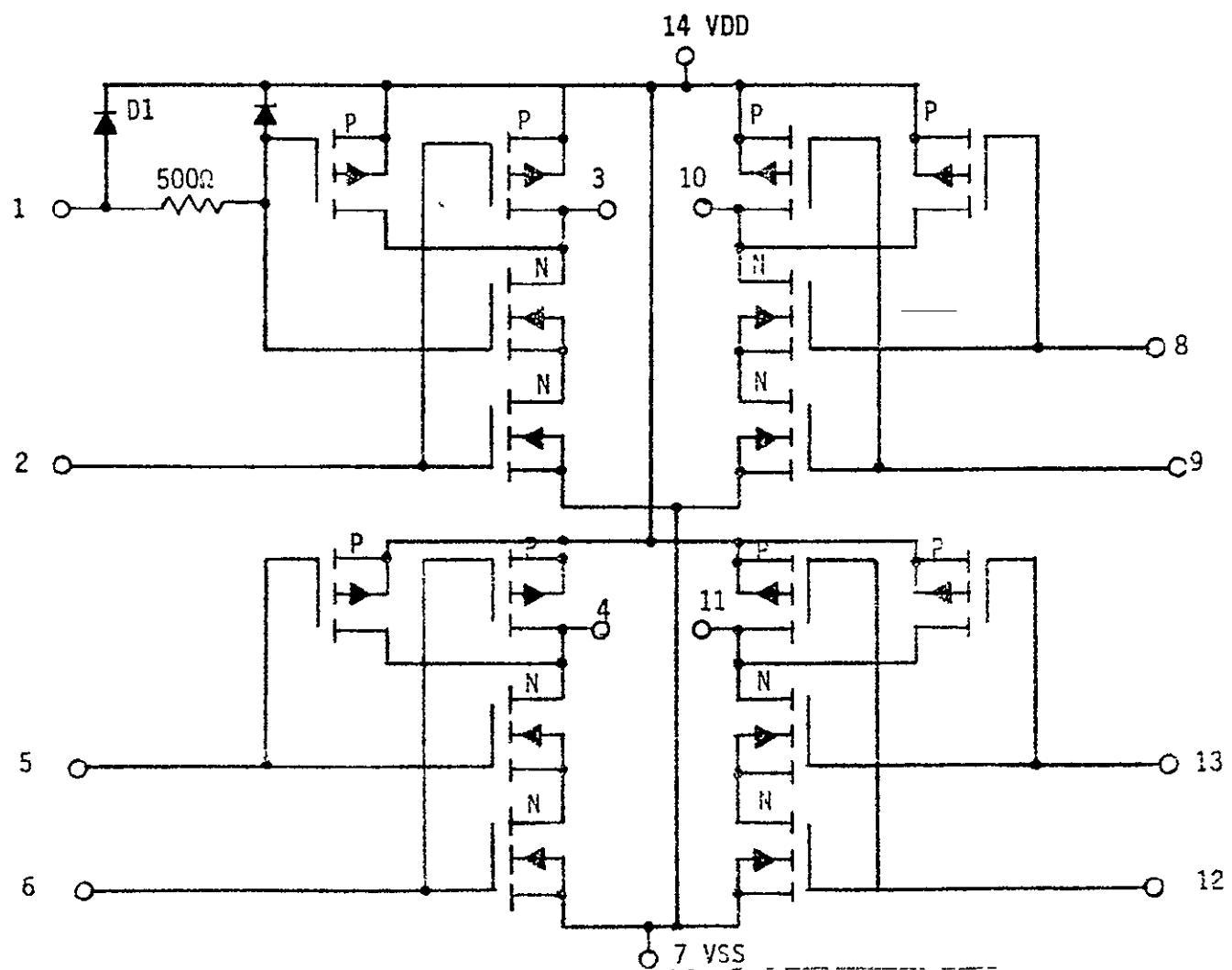
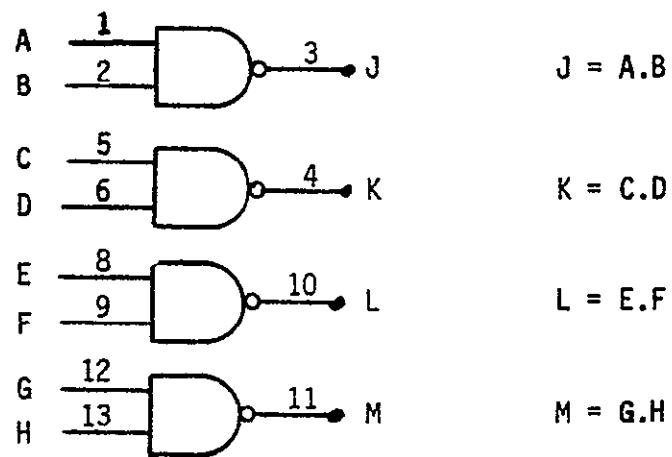


Fig. 5 - Logic and circuit diagrams for the CD4011A.

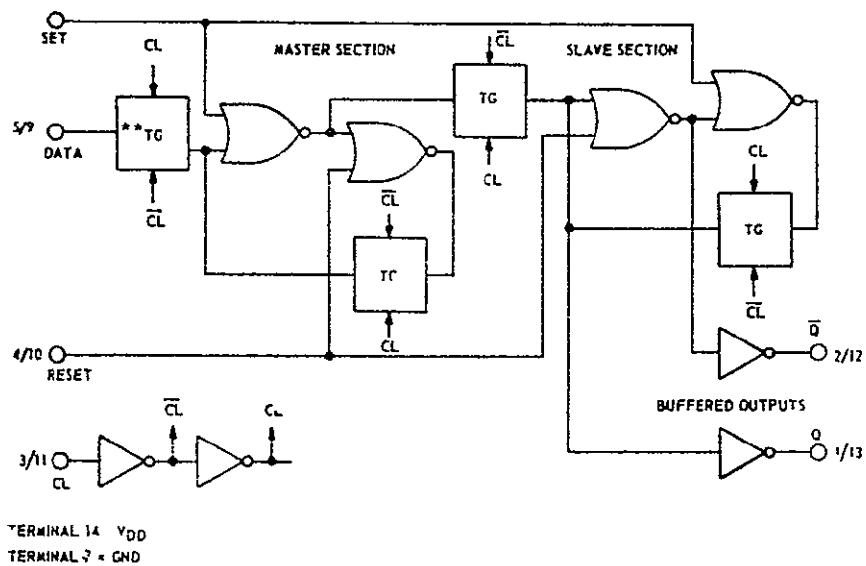


Fig. 6 - Logic and circuit diagrams for the CD4013A. (Page 1 of 2 pages.)

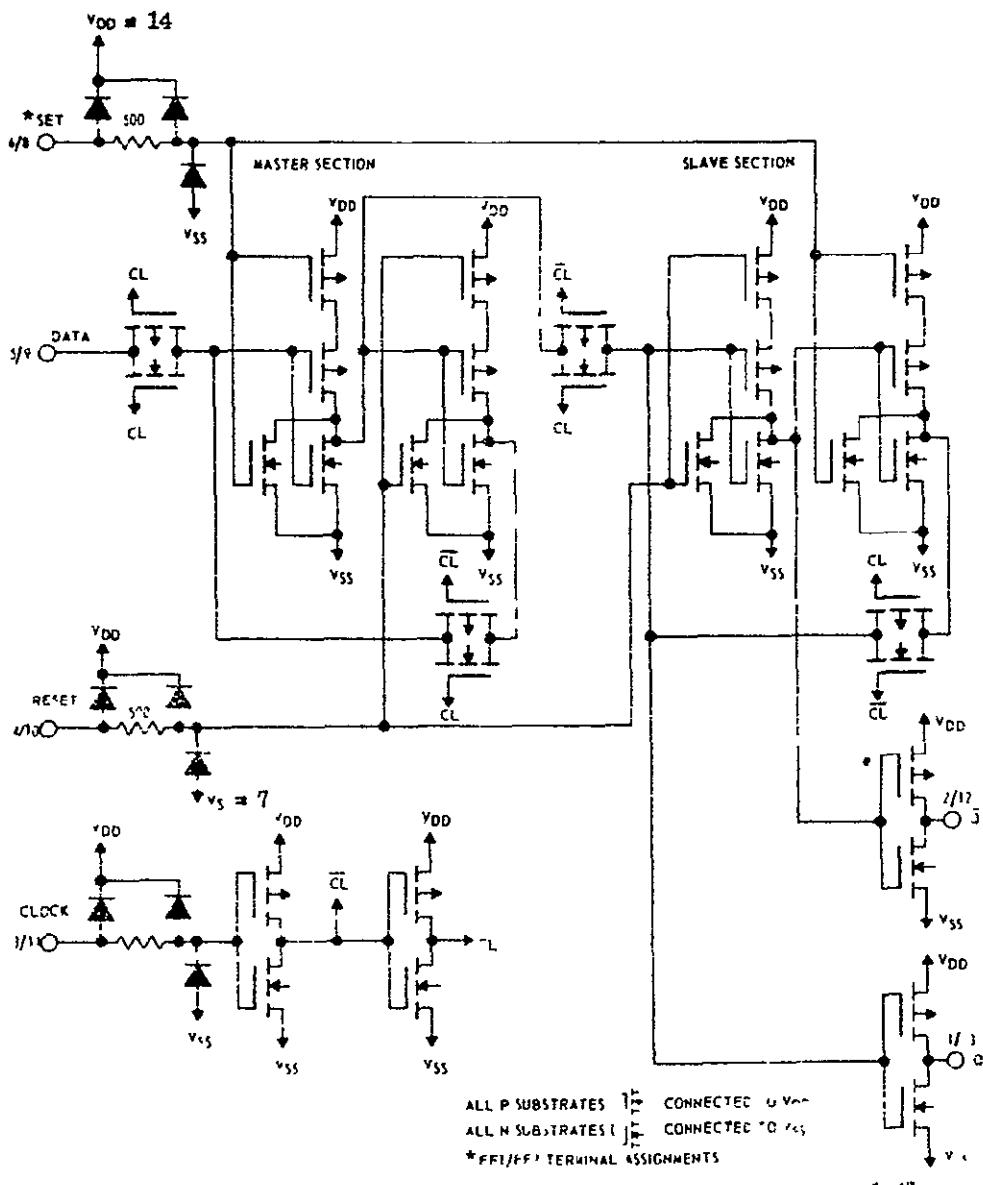


Fig. 6 - Logic and circuit diagrams for the CD4013A. (Page 2 of 2 pages.)

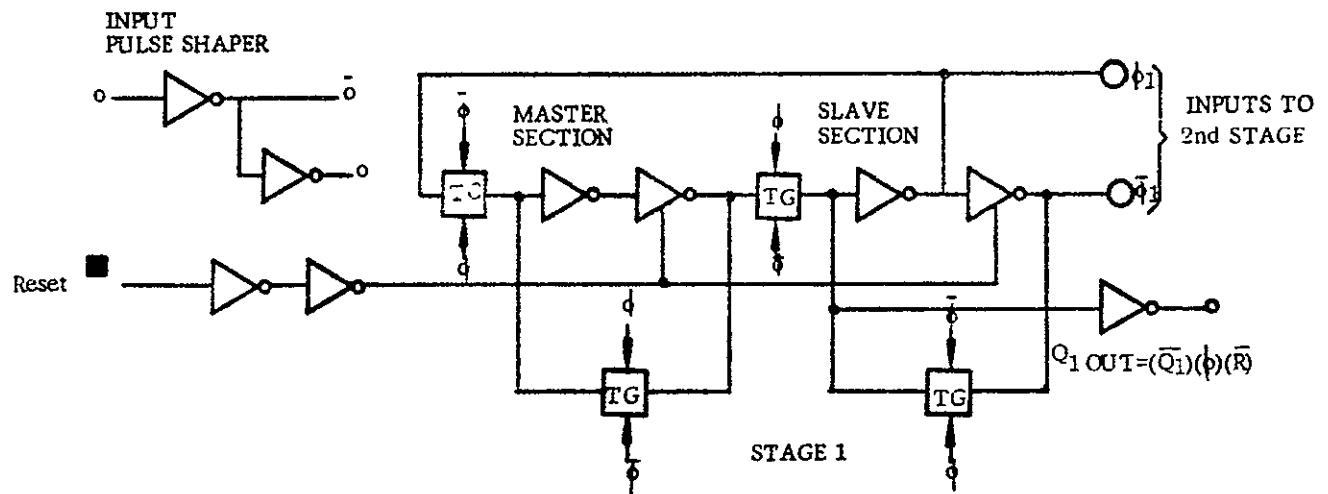
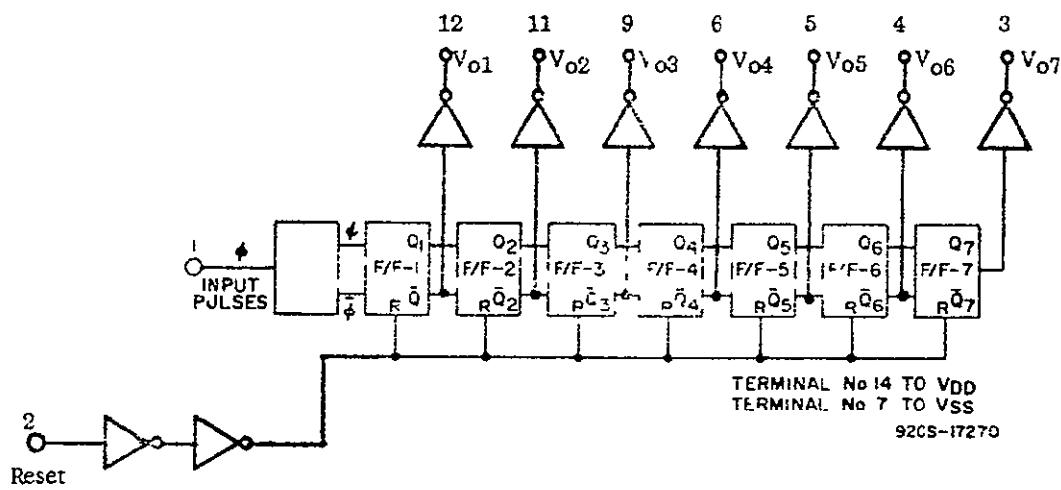
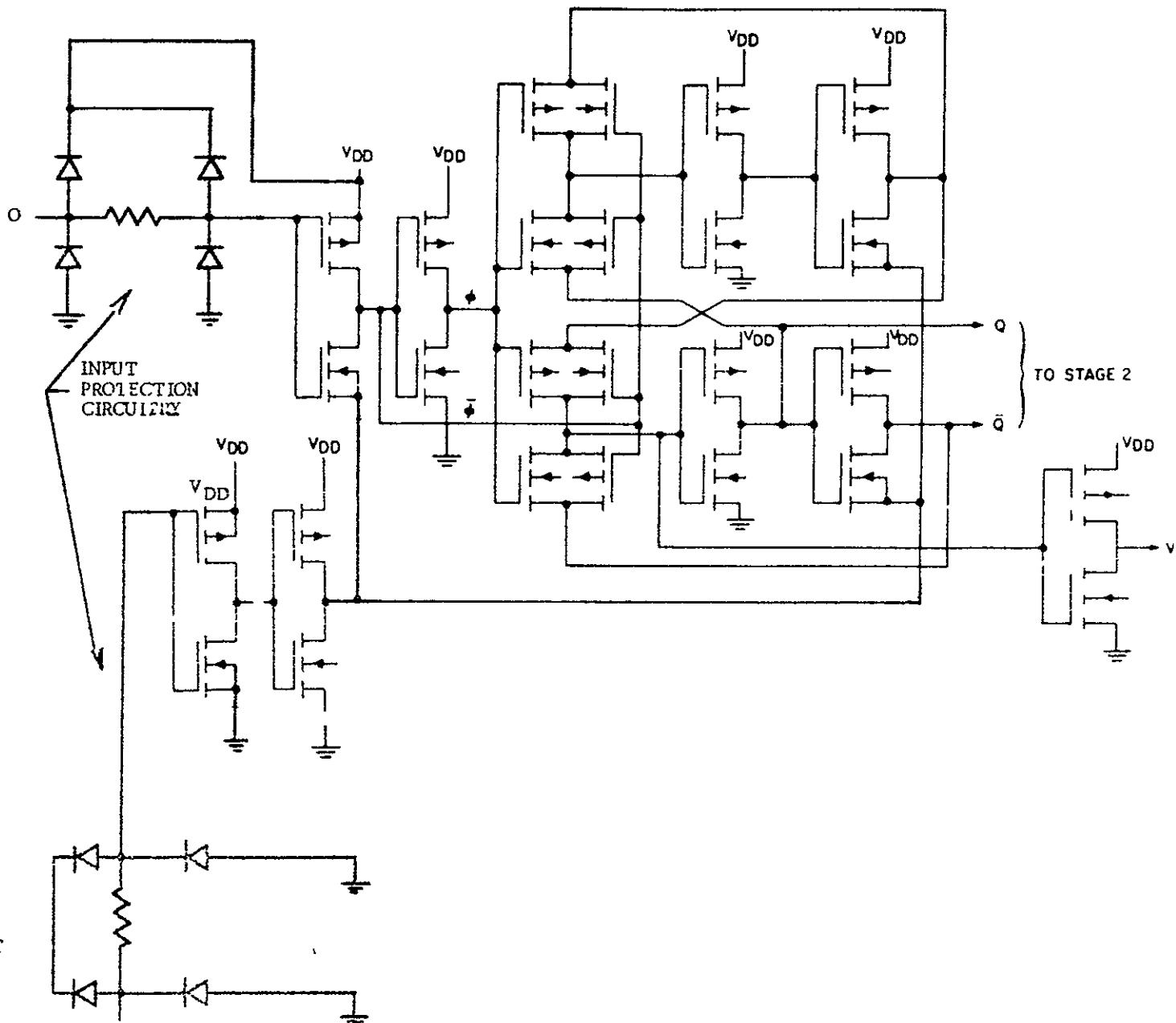


Fig. 7 - Logic and circuit diagrams for the CD4024A. (Page 1 of 2 pages.)



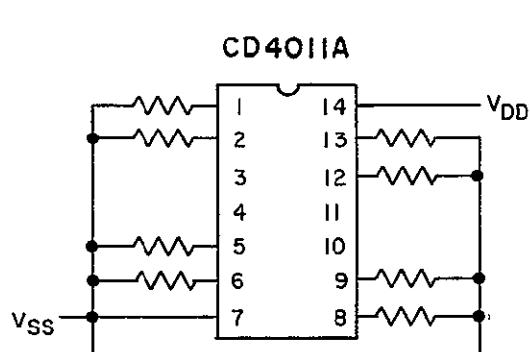
NOTE: SUBSTRATES FOR ALL "P" UNITS ARE CONNECTED TO V_{DD}
SUBSTRATES FOR ALL "N" UNITS, UNLESS OTHERWISE SHOWN, ARE CONNECTED TO GROUND.

Schematic diagram of Input Pulse Shaper and one of seven binary stages for CD4024A

Fig. 7 - Logic and circuit diagrams for the CD4024A. (Page 2 of 2 pages.)

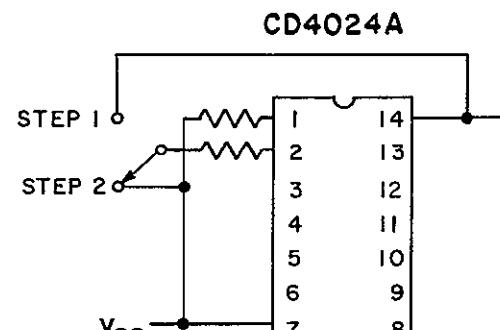
SECTION IV
TEST VOLTAGE AND BIAS

The choice of bias was dictated by the desire to further accelerate the life testing process by stressing the n-channel transistor to possibly the worst-case condition. The available evidence suggests that the n-channel transistor in CMOS microcircuits is the weak link when biased to the off condition (gate is low with respect to drain). The drain-to-source and drain-to-gate potentials set up under this bias accelerate movement of the positively charged (usually sodium) particles. These particles are thought to accumulate in the oxide, thereby neutralizing the effect of the negatively biased gate and setting up a mechanism for potential leakage. The biases used are shown in the pin connection diagrams of Fig. 8. The operating voltage was chosen as 12.5 volts dc to conform to the M-38510 specifications.



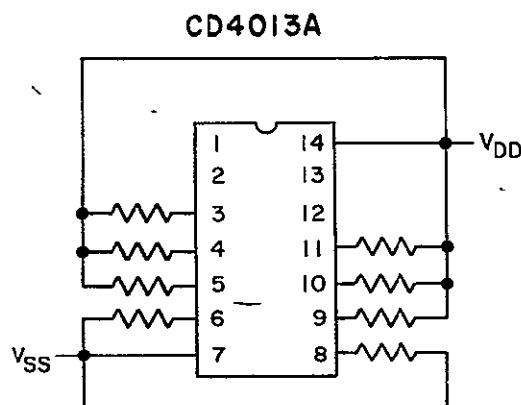
92CS-28638

ALL RESISTORS ARE 47KΩ



92CS-28637

ALL RESISTORS ARE 47KΩ



92CS-28636

ALL RESISTORS ARE 47KΩ

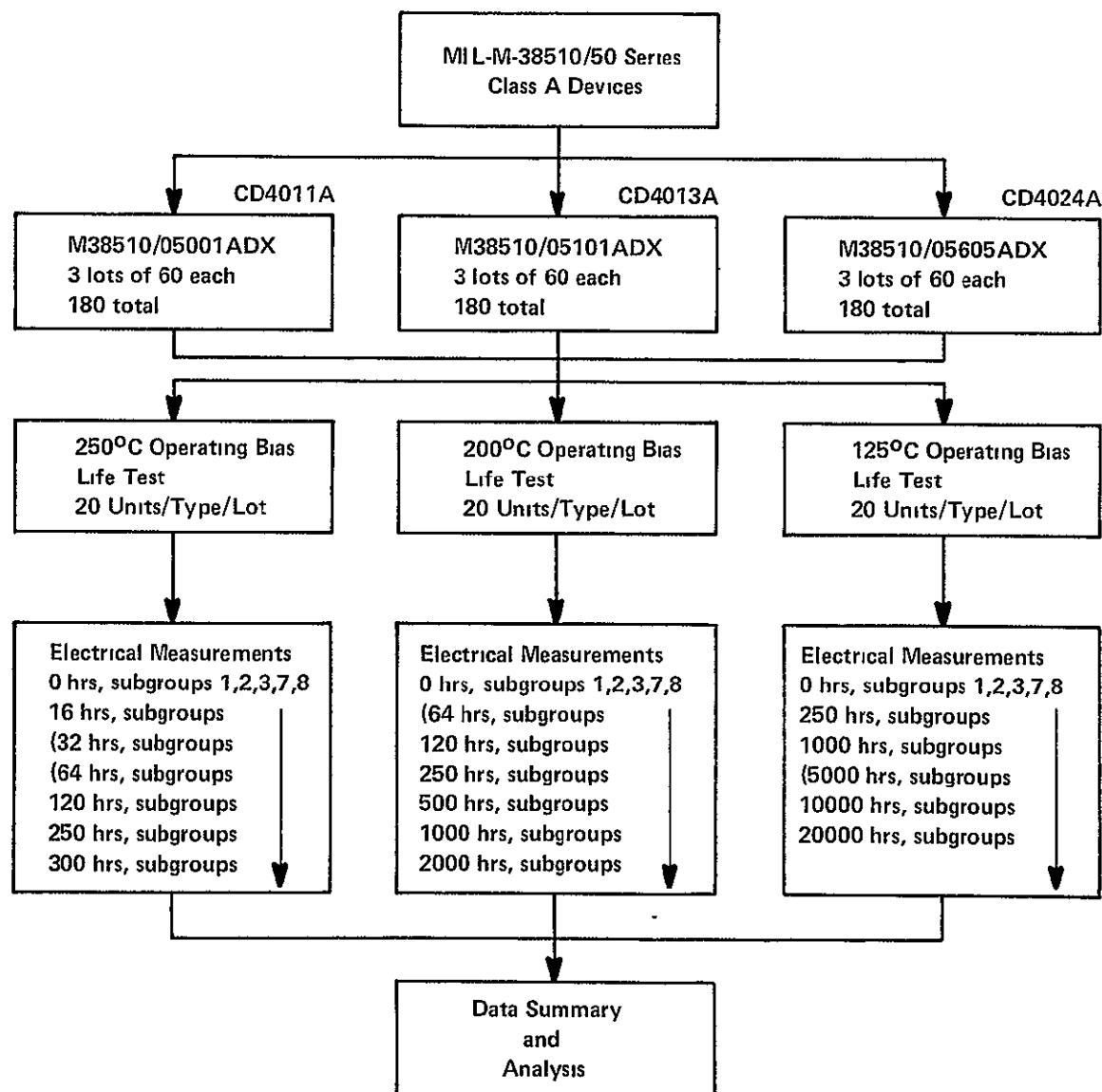
Fig. 8 - Bias connection diagrams.

SECTION V
THE TEST

The test matrix was developed and is shown in Table IV. Devices were selected from three lots in each type to represent broad process variations. The program encompasses 3 life-test temperatures. Each lot is represented by 20 test devices in each life test for a total of 60 test devices of each type. Each test sample of 20 test devices had, in addition, 5 control devices which were monitored at each measurement point together with the test devices, but were not life tested.

Prior to beginning of the contract, trial runs were started. Data from those runs prompted the introduction of more measurement points for the 250°C as well as the 200°C life test. The testing at each measurement point was broadened to include 125°C, and -55°C measurements.

Table IV – Test Matrix



SECTION VI

DATA PRESENTATION AND ANALYSIS

The test measurement results obtained in the course of this program were considered in three ways.

1. Data from the three life-test temperature cells (250°C, 200°C, and 125°C). This data includes failure attributes summary, parameter trend tables and curves, and failure rate versus time charts.
2. Results that require data from failure analysis. This report includes early failure analysis on some catastrophically failed devices.

Tables V, VI, and VII give the cumulative failures per type for each life-test temperature cell versus time. In an attempt to minimize the arbitrariness in the failure definition, the failure attributes data is presented in the following ways.

1. Column I. The failures are defined in accordance with the M38510/50 individual specifications limits as given in Table III of these specifications (Tables I, II, and III of this report). All failures are counted including the continuity failures. This data is not plotted.
2. Column II. Less continuity. The continuity failures are excluded from the count if the failure analysis reveals:
 - (a) burned-out metallization indicating possibility of external influence, (b) automated testing problems stemming from improper socket contact. The failure as in (b) is really a good device and is considered as such in subsequent measurement points.

TABLE V - SUMMARY OF FAILURE ATTRIBUTES
(CD4011A)

Temp.	Lot/Hrs	I				II				III						
		ALL FAILURES				LESS CONTINUITY				LESS MARGINAL LEAKAGE						
		<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>	<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>	<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>			
250°C	40	0/19	0/19	0/17	16/17	0/19	0/19	0/17	16/17	0/19	0/19	0/17	16/17			
	50	2/20	6/20	8/20	16/20	2/20	6/20	8/20	15/19	0/20	1/20	2/20	15/19			
	60	2/20	2/19	8/19	18/19	2/20	2/19	8/19	0/1	0/20	0/19	5/19	0/1			
Total		4/59	8/58	16/56	50/56	4/59	8/58	16/56	31/37	0/59	1/58	7/56	31/37			
%		7	14	29	89	7	14	29	84	0	2	13	84			
≈ 200°C 88	Temp.	<u>64</u>	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>	<u>64</u>	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>	<u>64</u>	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>
		43	0/20	0/20			0/20	0/20			0/20	0/20				
		53	1/20	1/20	1/20		1/20	1/20	1/20		0/20	0/20	1/20			
Total		3/60	3/60	3/40			1/19	1/20	1/20		0/19	0/20	0/20			
%		5	5	7.5			2/59	2/60	2/40		0/59	0/60	1/40			
125°C	Temp.	<u>168</u>	<u>500</u>	<u>1000</u>			<u>168</u>	<u>500</u>	<u>1000</u>		<u>168</u>	<u>500</u>	<u>1000</u>			
		40	0/20	0/20	0/20		0/20	0/20	0/20		0/20	0/20	0/20			
		50	0/20	0/20	2/20		0/20	0/20	0/18		0/20	0/20	0/18			
Total		0/60	0/60	2/60			0/20	0/20	0/58		0/60	0/60	0/58			
%		0	0	3			0	0	0		0	0	0			

TABLE VI - SUMMARY OF FAILURE ATTRIBUTES
(CD4013A)

Temp.	Lot/Hrs	I			II				III			
		<u>ALL FAILURES</u>			<u>LESS CONTINUITY</u>				<u>LESS MARGINAL LEAKAGE</u>			
		<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>		<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>		
250°C	41	2/20	10/20				2/20	8/18			0/20	1/18
	81	5/20	7/20	15/15			5/20	6/19	15/15		5/20	5/19
	21	2/20	12/20				1/19	11/19			0/19	6/19
Total		9/60	29/60	15/15			8/59	25/56	15/15		5/59	12/56
%		15	48	100			14	45	100		8	21
												100

Temp.	Lot/Hrs	<u>64</u>	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>	<u>64</u>	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>	<u>64</u>	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>
200°C	83	1/20	4/20	5/20	8/20		0/19	1/17	1/16	3/15		0/19	1/17	1/17	2/15	
	43	0/20	2/20	2/20	2/20		0/20	0/18	0/18	0/18		0/18	0/18	0/18	0/18	
Total		1/40	6/40	7/40	10/40		0/39	1/35	1/34	3/33		0/37	1/35	1/35	2/33	
%		5	15	18	25		0	3	3	9		0	3	3	6	

Temp.	Lot/Hrs	<u>250</u>	<u>1000</u>	<u>250</u>	<u>1000</u>	<u>250</u>	<u>1000</u>
125°C	42	0/20		0/20		0/20	
	82	0/20		0/20		0/20	
	22	0/20		0/20		0/20	
Total		0/60		0/60		0/60	
%		0		0		0	

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TABLE VII - SUMMARY OF FAILURE ATTRIBUTES
(CD4024A)

Temp.	Lot/Hrs	I				II				III								
		<u>ALL FAILURES</u>				<u>LESS CONTINUITY</u>				<u>LESS MARGINAL LEAKAGE</u>								
		<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>			<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>			<u>16</u>	<u>32</u>	<u>64</u>	<u>120</u>	
250°C	51	2/20	13/19					2/20	12/18					1/20	11/18			
	61	8/20	15/20					6/18	13/18					4/18	13/18			
	32	7/19	10/18	18/18				7/19	10/18	18/18				7/19	9/18	18/18		
Total		17/59	38/57	18/18				15/57	35/54	18/18				12/57	33/54	18/18		
%		28	66	100				26	65	100				21	65	100		
200°C	53	0/20	3/20	11/19				64	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>		64	<u>120</u>	<u>250</u>	<u>500</u>	<u>1000</u>
	33	0/20	1/20	7/20				0/20	3/20	11/19				0/20	2/20	7/19		
	63	3/20	3/20	11/20				0/20	1/20	7/20				0/20	1/20	7/20		
Total		3/60	7/60	29/59				3/60	7/60	29/59				0/60	3/60	21/59		
%		5	12	49				5	12	49				0	5	36		
125°C	52	0/20	3/20					250	<u>1000</u>					250	<u>1000</u>			
	34	0/20	3/20					0/20	3/20					0/20	0/20			
	62	3/20	3/20					0/20	0/17					0/20	0/17			
Total		3/60	9/60					3/20	3/20					0/20	0/20			
%		5	15					5	11					0	0			

John

3. Column III. Less marginal leakage. The marginal leakage devices are subtracted from the count of Column II. The marginal leakage failures are those which have their measured leakages below the clamped values. The clamped values for each type are given in the table below; they are determined by the automated test set up.

Type	I_{SS}		I_{1H}/I_{1L}
	25°C	125°C	25°C
CD4011A	159.8 nA	1598 nA	15.98 nA
CD4013A	1598 nA	15.98 μA	15.98 nA
CD4024A	1598 nA	15.98 μA	15.98 nA

It is believed that in presenting the data this way, devices which indicate a higher probability of becoming non-functional in the application will be segregated from those devices which have leakage increases but that would not affect system functioning.

The data tabulated in Tables V, VI and VII, "Summary of Failure Attributes" has been plotted in Figs. 9 through 16. The graph paper used is log normal since this type of accelerated testing is expected to have a log-normal distribution. For the log-normal distribution, the failure rate at any given time can be calculated. The curve allows one to get a quick indication of whether the failure rate is increasing or decreasing. In addition, this type of plot provides the ability to determine the "freak" part, if it exists, and the main part of the distribution.

Figs. 9 and 10 indicate the failure rate at 250°C versus time. Some observations can be made at this point in regard to these results:

1. The percent of the CD4011A is significantly lower than those of the CD4013A or CD4024A.

% CUMULATIVE FAILURES

46 8080

K-E PROBABILITY X 3 LOG CYCLES
KEUFFEL & ESSER CO MADE IN U.S.A.

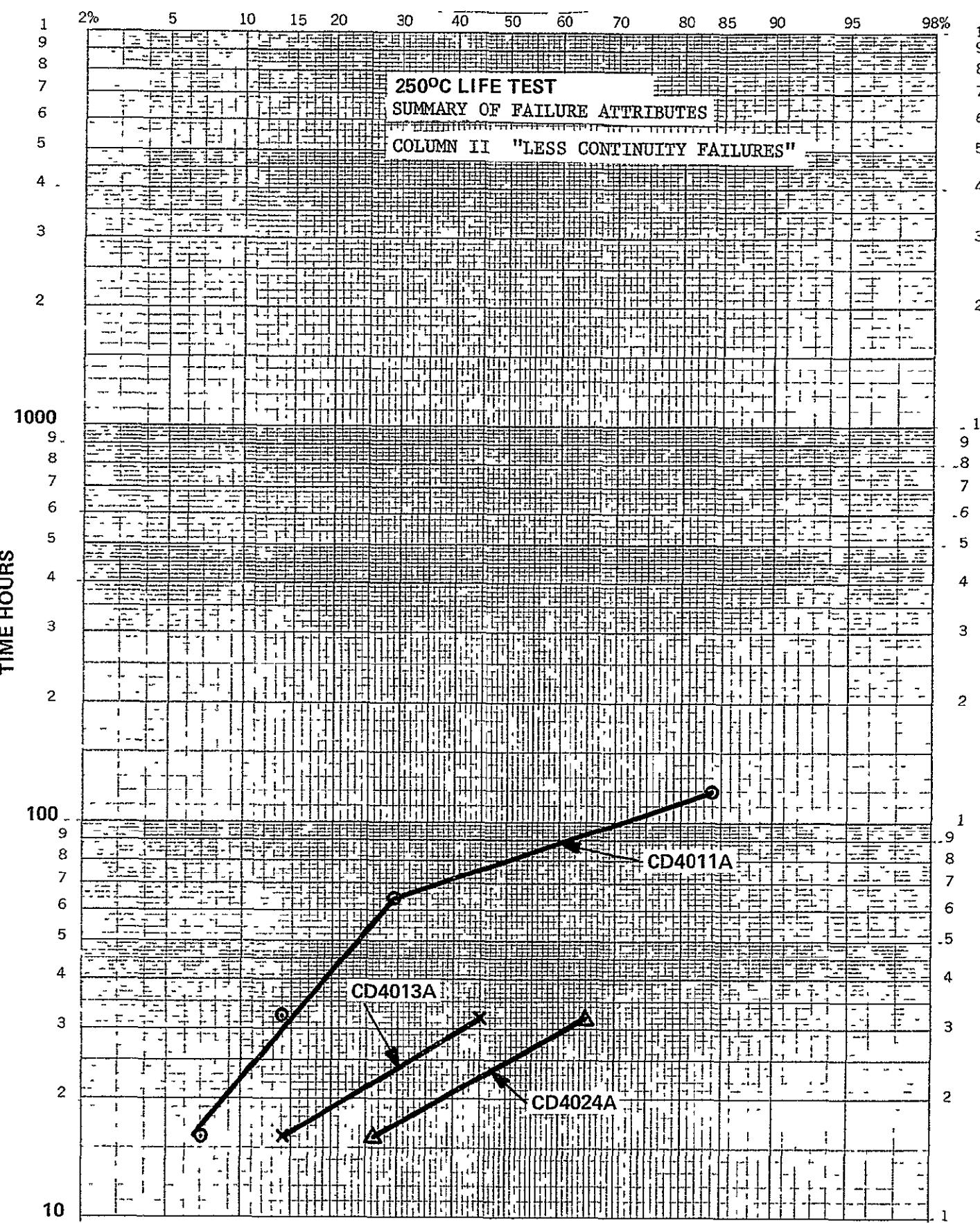


Fig. 9

% CUMULATIVE FAILURES

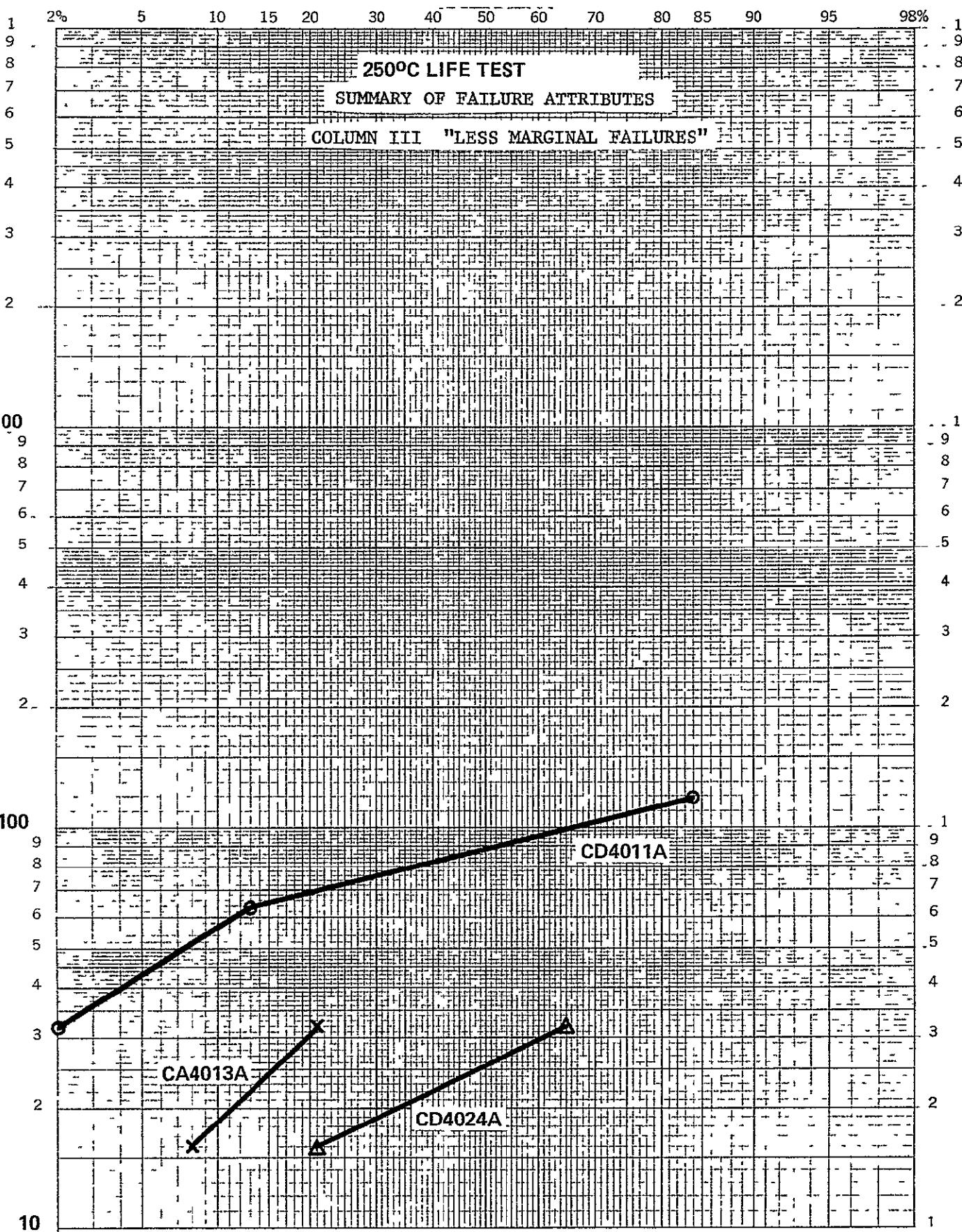


Fig. 10

% CUMULATIVE FAILURES

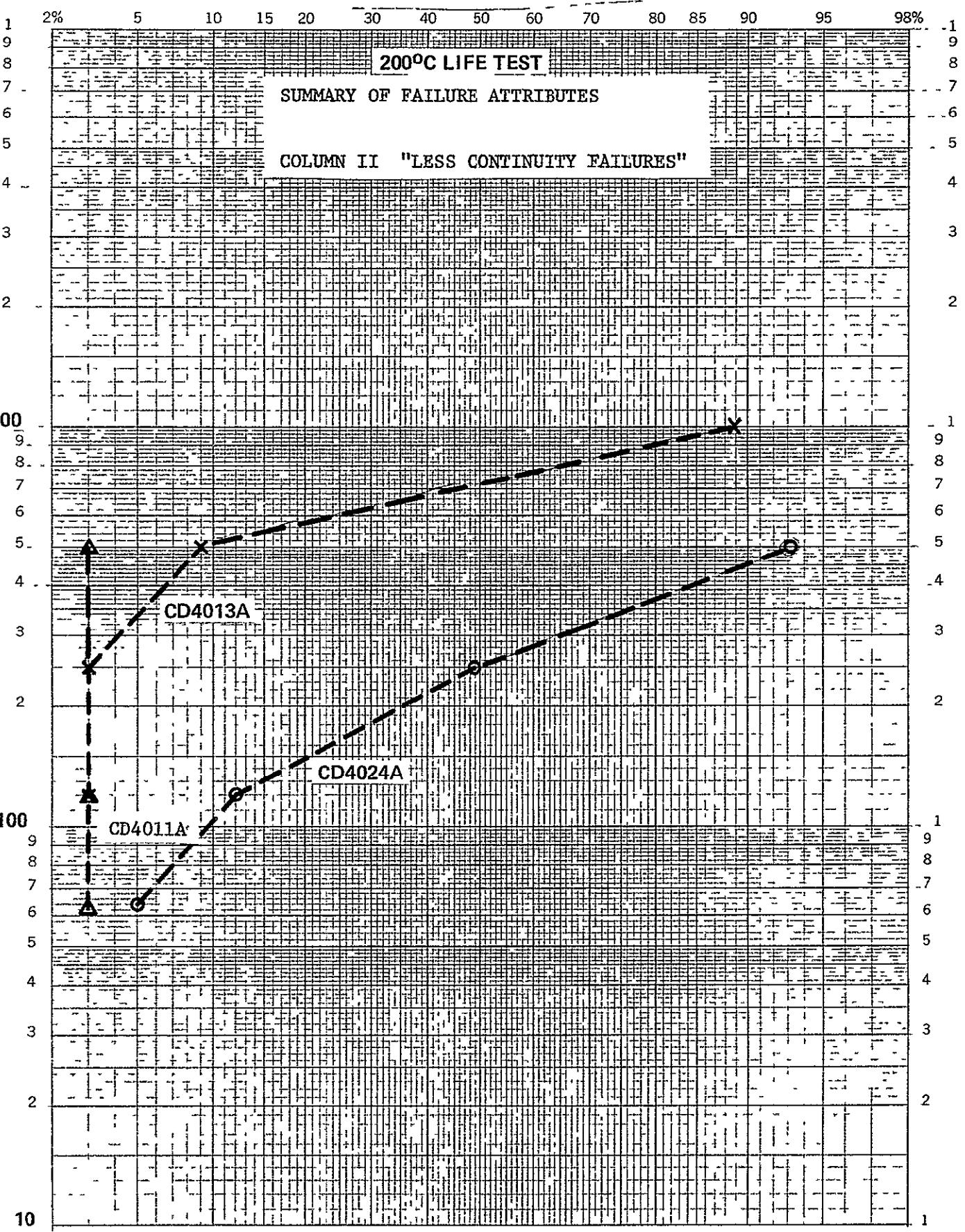


Fig. 11

% CUMULATIVE FAILURES

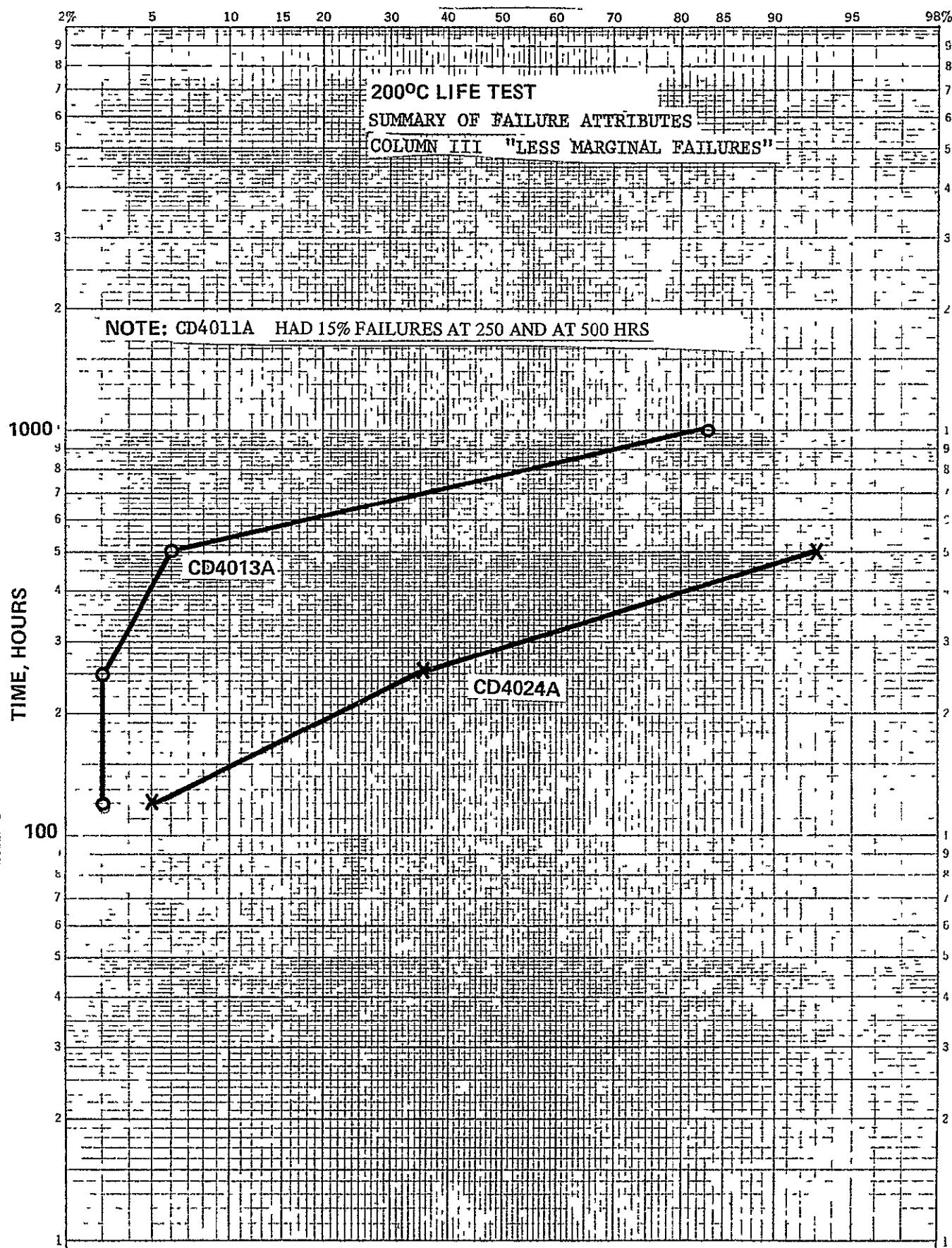


Fig. 12

46 8080

K&E
PROBABILITY X 3 LOG CYCLES
KEIFFEL & ESSER CO MADE IN U.S.A.

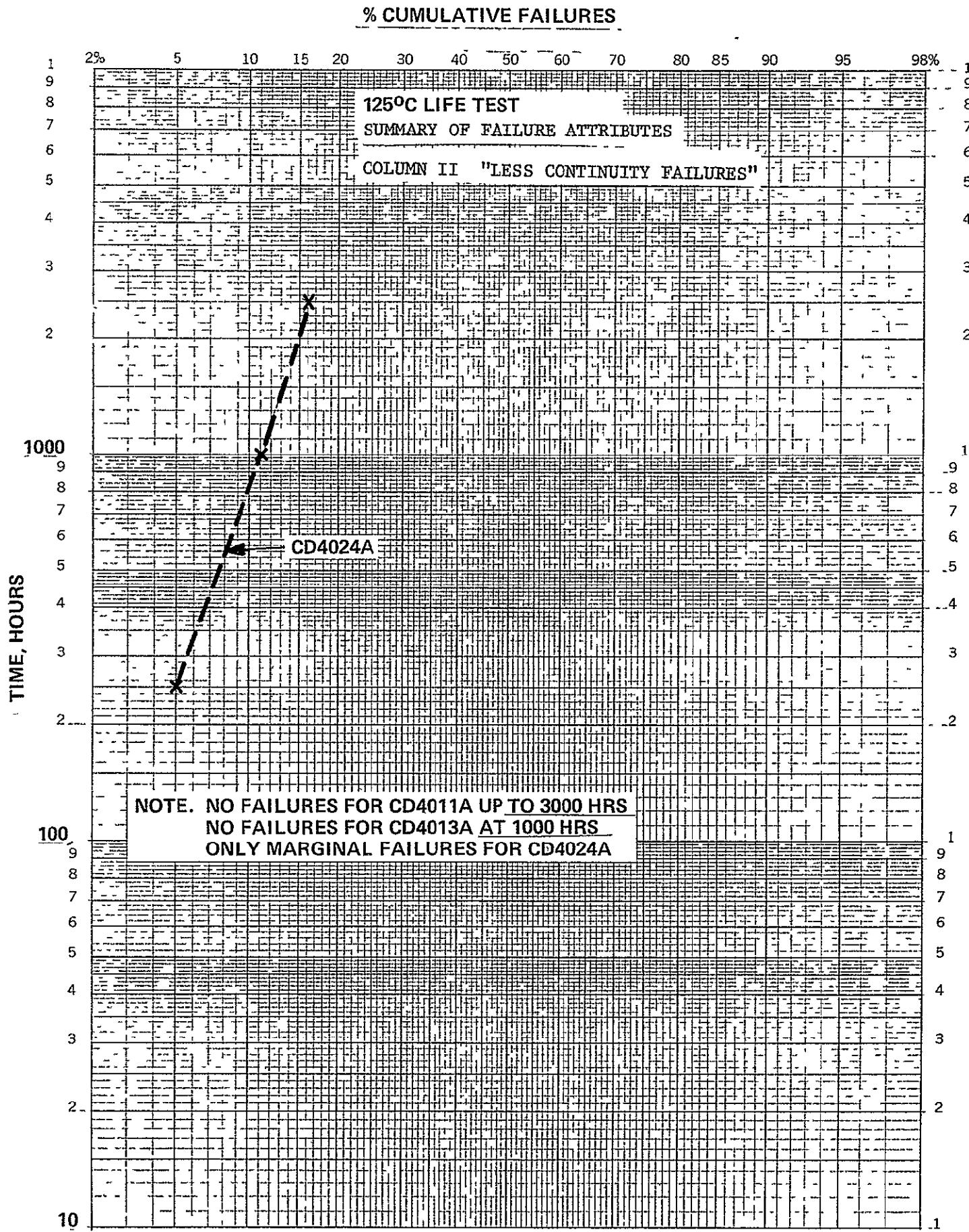


Fig. 13

% CUMULATIVE FAILURES

46 8080

PROBABILITY X 3 LOG CYCLES
KEUFFEL & ESSER CO. MADE IN U.S.A.

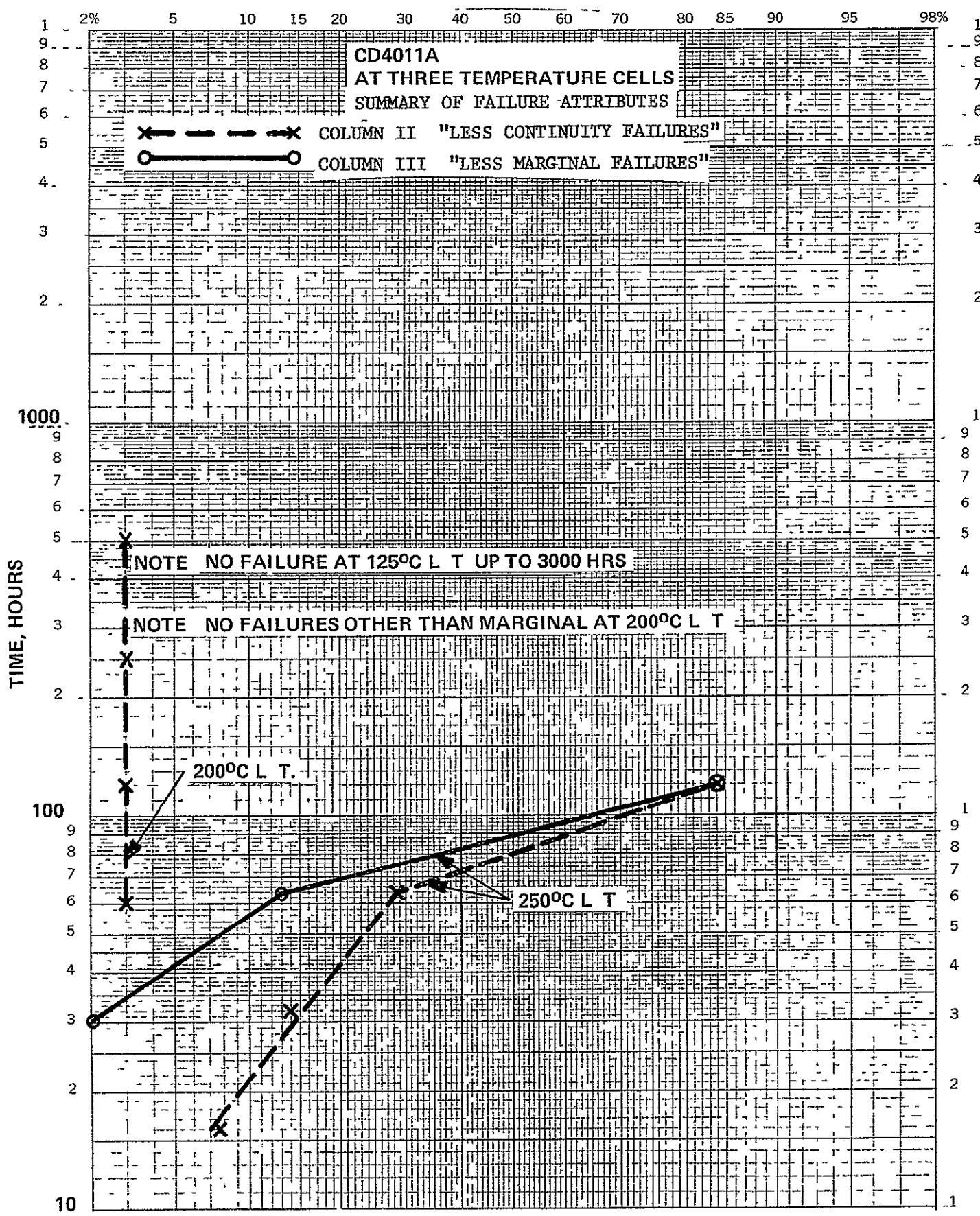


Fig. 14

% CUMULATIVE FAILURES

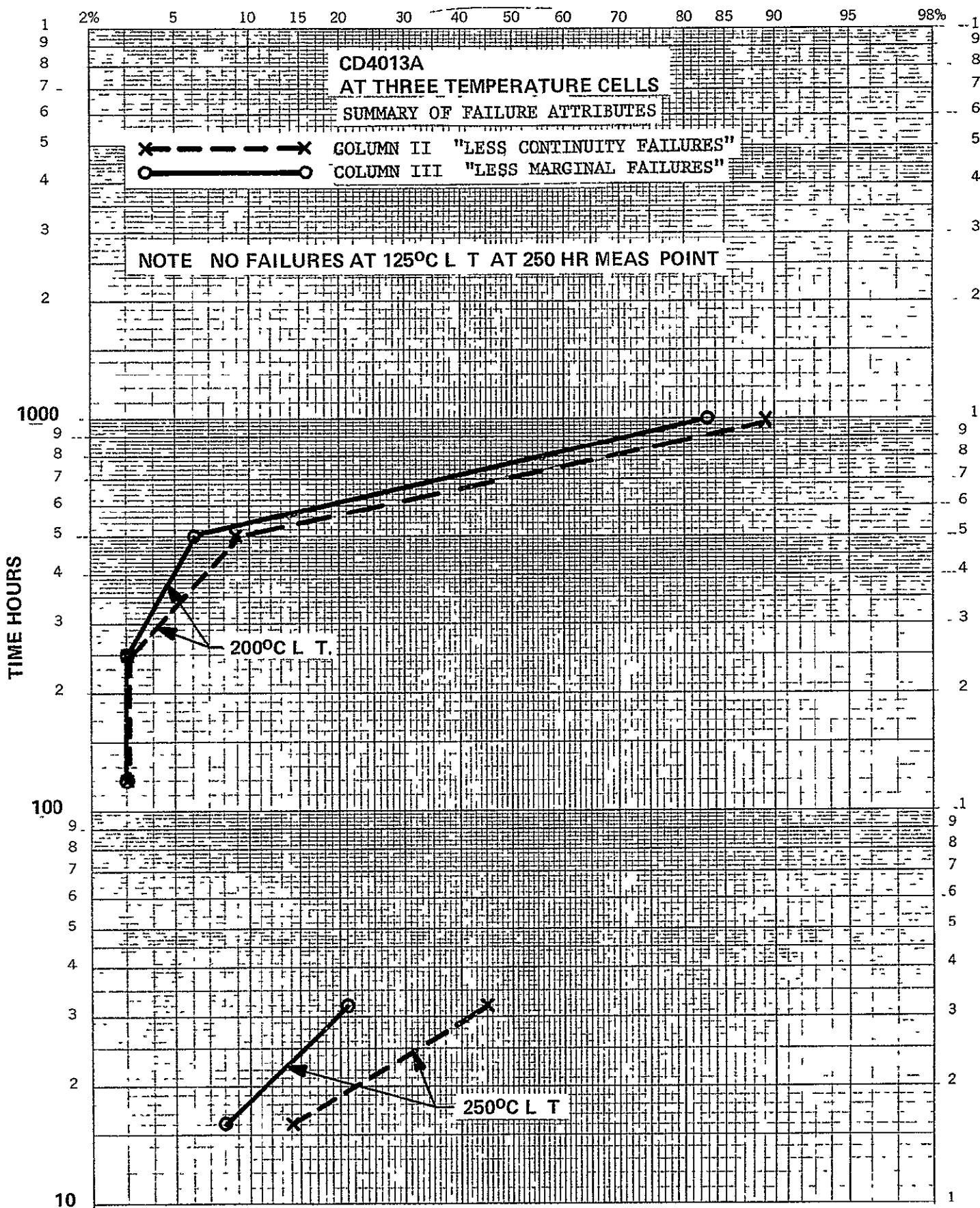


Fig. 15

% CUMULATIVE FAILURES

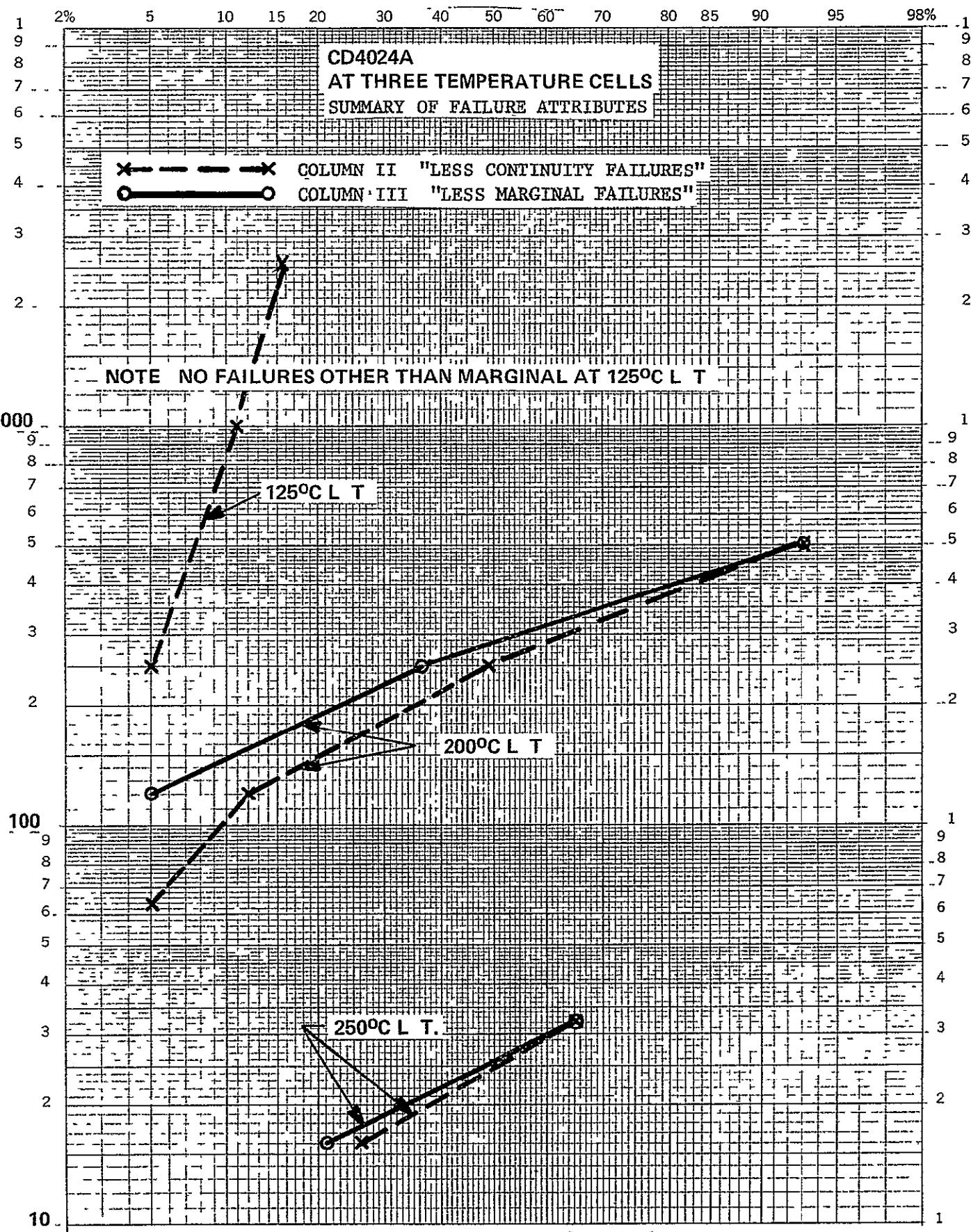


Fig. 16

46 8080

PROBABILITY X 3 LOG CYCLES
KEUFFEL & ESSER CO MADE IN U.S.A.

2. There is a noticeable increase of CD4011A failure rate and a change in distribution between the 64 hour and the 120 hour measurement points, indicating that perhaps some as yet unidentified threshold has been exceeded.
3. The difference in failure rates between CD4011A, CD4013A and CD4024A suggests a desirability to consider the chip size and/or the complexity of a microcircuit as a possible factor influencing failure rates. This observation supports a conclusion arrived at in another report prepared by RCA Solid State Division for the RADC, Contract #F30602-73-C-0282.
4. The high percentage of failures observed during the early measurement points (16 hours and 32 hours) as well as significant failure-rate changes between the 64 hour and the 120 hour measurement points suggest a desirability of even more frequent measurement points. This is especially applicable to the 250°C life test. Some improvement in that direction has been implemented, following consequent recommendation, by introducing the 32 hour and the 64 hour measurement points for the 250°C life test and the 64 hour measurement point for the 200°C life test.
5. For the present, we are inclined not to recommend the 250°C temperature for the accelerated life test for the following reasons:
 - a. The three CMOS device types listed, CD4011A, CD4013A, and CD4024A did not meet the requirements for Class A conformance testing delineated in MIL Std 883A Method 5005.3, Table II(a), Subgroup 5; 250°C testing.
 - b. There is strong evidence that a threshold may have been exceeded.
 - c. Sample selection presents difficulty because solder-dipped leads, the standard finish for Class A devices, cannot be used at such high temperature.
 - d. Presently available high-temperature carriers are too brittle and present considerable handling problems in the life test racks as well as the automated test equipment.

Figs 11 through 16 are included to give an insight into the failure rates at the 200°C life test and the 125°C life test. Although the early measurement points suggest lower failure rates, no definite statements to that effect can be made until data from more measurement points is available.

Tables VIII, IX, and X give for the 250°C test cell the means, the standard deviation, and the high value at each measurement point on the per lot basis for the surviving devices at two measurement temperatures, 25°C and 125°C. Figs. 17, 18, and 19 represent plots of mean averaged over three lots for each type and at two temperatures. The surviving units are defined as those the readings of which did not reach the clamped values. Clamped values are the upper limits of the instrument range to which the automated measurement system is set. The table on page 31 gives clamped values for I_{SS} for each type at 25°C and 125°C measurement temperatures.

There are three I_{SS} tests in the M58510/05001ADX (CD4011A) specifications. The results of all three of these tests were used in the parameter trend tables and graphs. From the M38510/05101ADX (CD4013A) and M38510/05605ADX (CD4024A) test results, three I_{SS} tests for each type were selected to avoid presentation of repetitious data. The selected I_{SS} test data indicated the greatest parameter shift. The leakage versus time plot indicates a fair stability for the surviving CD4011A, but show considerable movement for the CD4013A and CD4024A. The 25°C measurements seems to track the 125°C measurements, indicating that for the purpose of observing leakage shift, both measurement temperatures are equally effective.

TABLE VIII - I_{SS} Trend with Time for the M38510/05001ADX (CD4011A)

Time		0 Hrs			16 Hrs			32 Hrs			64 Hrs			120 Hrs			
Lot #	Test #	50	51	52	50	51	52	50	51	52	50	51	52	50	51	52	
	Unit	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	
25°C Measurements	5361740	Mean	0.17	0.16	0.44	0.75	1.1	2.7	0.83	1.07	1.39	1	1.04	1.27	0.68	10.8	0.37
		S D	0.27	0.36	0.59	0.25	0.76	0.19	0.18	0.13	0.17	0.20	0.09	0.33	0.3	30.8	0.32
		H V	0.7	1	1.3	1.1	1.1	3	1.2	1.2	1.6	1.4	1.3	1.5	159.8	108.4	1.2
6153050	6153050	Mean	0.65	1.01	1.37	2	1.32	3.4	3.73	3.22	5.55	3.55	3.48	5.21	2.2	17.6	0.70
		S D	0.4	0.1	0.16	2.2	0.44	0.56	6.31	1.28	7.87	2.3	0.91	3.8	2.89	11.9	0.14
		H V	1.2	1.2	1.7	3.1	3.1	5.6	30.4	8.2	38	11.8	6.3	19.7	10.8	3	0.9
6153060	6153060	Mean	0.07	0.88	1.13	0.9	1.4	3.4	0.67	1.2	1.55	1.61	1.93	2.23			
		S D	0.09	0.1	0.12	1.2	1.1	2.3	0.35	0.32	0.34	0.78	0.54	0.75			
		H V	0.2	1	1.4	5.7	5.5	12.5	1.2	2	2.5	3.5	3.1	4.7			
125°C Measurements	5361740	Unit	μ A														
		Mean	100.2	67	74	125.7	100.3	72.1	131.7	96.9	73.4	134.6	89.8	72.8	301.4	457.5	115
		S D	19.6	39.7	16	26.4	19	14.6	28.4	20	15	33.4	23.5	15.6	361.1	415.1	24.4
6153050	6153050	H V	136	109	98	172	132	97	188	137	103	193	133	104	1393	751	158
		Mean	143.7	64.1	126.2	175.1	103.8	130	180.1	97.1	125.2	196.1	89.1	230.8	259	395.2	103.6
		S D	53.3	36.6	31	47.7	26.2	36.5	53	17.6	39.7	60.4	22.8	295.2	137.1	509.2	30.8
6153060	6153060	H V	222	103	197	265	124	197	284	125	200	292	117	1086	499	227	176
		Mean	63	79.6	51.3	76.7	79.3	48.5	77.1	78.6	49	45	42.8	27.7			
		S D	26	26.4	18.5	28	25.1	19.8	30.1	25.7	19.22	21	18.2	15.3			
		H V	138	140	91	134	136	84	132	136	83	86	80	55			

TABLE IX – I_{SS} Trend with Time for the M38510/05101ADX (CD4013A)

Time		0 Hrs			16 Hrs			32 Hrs			64 Hrs			120 Hrs
Lot #	Test #	50	55	60	50	55	60	50	55	60	50	55	60	
	Unit	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	
25°C Measurements	5393021	Mean	00	00	00	11	08	14	00	00	05			
		S D	00	00	00	46	08	10	00	00	10			
		H V	00	00	00	200	30	30	00	00	30			
	6123241	Mean	00	00	00	00	05	12	00	00	01			
		S D	00	00	00	00	08	11	00	00	02			
		H V	00	00	00	00	30	30	00	00	10			
	6153081	Mean	00	00	00	08	16	20	410	870	950	310	318	398
		S D	00	00	00	24	26	26	1400	360	3900	890	117	137
		H V	00	00	00	70	110	110	5700	1500	1600	330	44-7	50-7
125°C Measurements	5393021	Unit	μ A											
		Mean	0.093	0.07	0.092	0.27	0.12	0.19	0.67	2.5	2.4			
		S D	0.013	0.015	0.013	0.65	0.01	0.013	2.5	3.5	2.8			
		H V	0.12	0.12	0.12	30	0.13	0.14	110	130	82			
	6123241	Mean	0.11	0.12	0.12	0.28	0.19	0.21	0.08	110	0.13			
		S D	0.01	0.009	0.01	0.75	0.36	0.46	0.02	0.08	0.1			
		H V	0.13	0.13	0.13	35	17	22	0.13	0.42	0.52			
	6153081	Mean	0.072	0.074	0.074	0.24	0.57	0.64	0.84	0.5	0.53	0.58	0.28	0.35
		S D	0.009	0.007	0.008	0.54	1.2	1.4	2.4	1.1	1.2	0.61	0.41	0.5
		H V	0.09	0.09	0.09	23	45	54	9.1	35	38	16	11	13

TABLE X – I_{SS} Trend with Time for the M38510/05605ADX (CD4024A)

Time		0 Hrs			16 Hrs			32 Hrs			64 Hrs			120 Hrs
Lot #	Test #	60	63	67	60	63	67	60	63	67	60	63	67	
		nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	nA	
25°C Measurements	6201051	Mean	45.81	53.35	55.8	33.4	35.7	34.2	41.7	103.7	82.3			
		S D	109.36	110.98	110.57	129	125.2	123	96.6	246.3	177.5			
		H V	418	417	418	565	564	555	578	580	565			
	6201061	Mean	1.11	3.35	2.88	0	9.6	8.75	11	12	12			
		S D	1.11	2.39	2.86	0	0.7	1.9	24	24	23			
		H V	4	11	13	0	11	16	114	113	112			
	6202232	Mean	2.31	4	2.25	1.42	10.85	8.4	20	20	17.2	782	779	761
		S D	5	5.63	1.1	5.95	6	0.95	29	27.8	26.1	287	285	293
		H V	23	27	4	26	37	9	99	103	101	1160	1153	1142
125°C Measurements	6201051	Unit	μ A											
		Mean	0.42	0.54	0.54	0.70	0.77	0.73	1.2	1.2	1.9			
		S D	0.61	0.83	0.83	1.86	1.89	1.84	1.7	1.7	1.4			
	6201061	H V	2.34	2.96	2.95	8.4	8.41	8.41	6.03	5.76	5.24			
		Mean	0.18	0.21	0.21	0.17	0.19	0.18	3	3	3			
		S D	0.06	0.10	0.10	0.06	0.11	0.12	5	4	4			
	6202232	H V	0.37	0.55	0.56	0.29	0.28	0.28	0.5	0.49	0.50			
		Mean	0.12	0.12	0.12	0.24	0.22	0.22	0.45	0.44	0.43	7.58	All clamped	
		S D	0.02	0.02	0.02	0.29	0.27	0.27	0.50	0.48	0.47	2.75		
		H V	0.2	0.21	0.21	1.4	1.35	1.32	17	17	16	9.39		

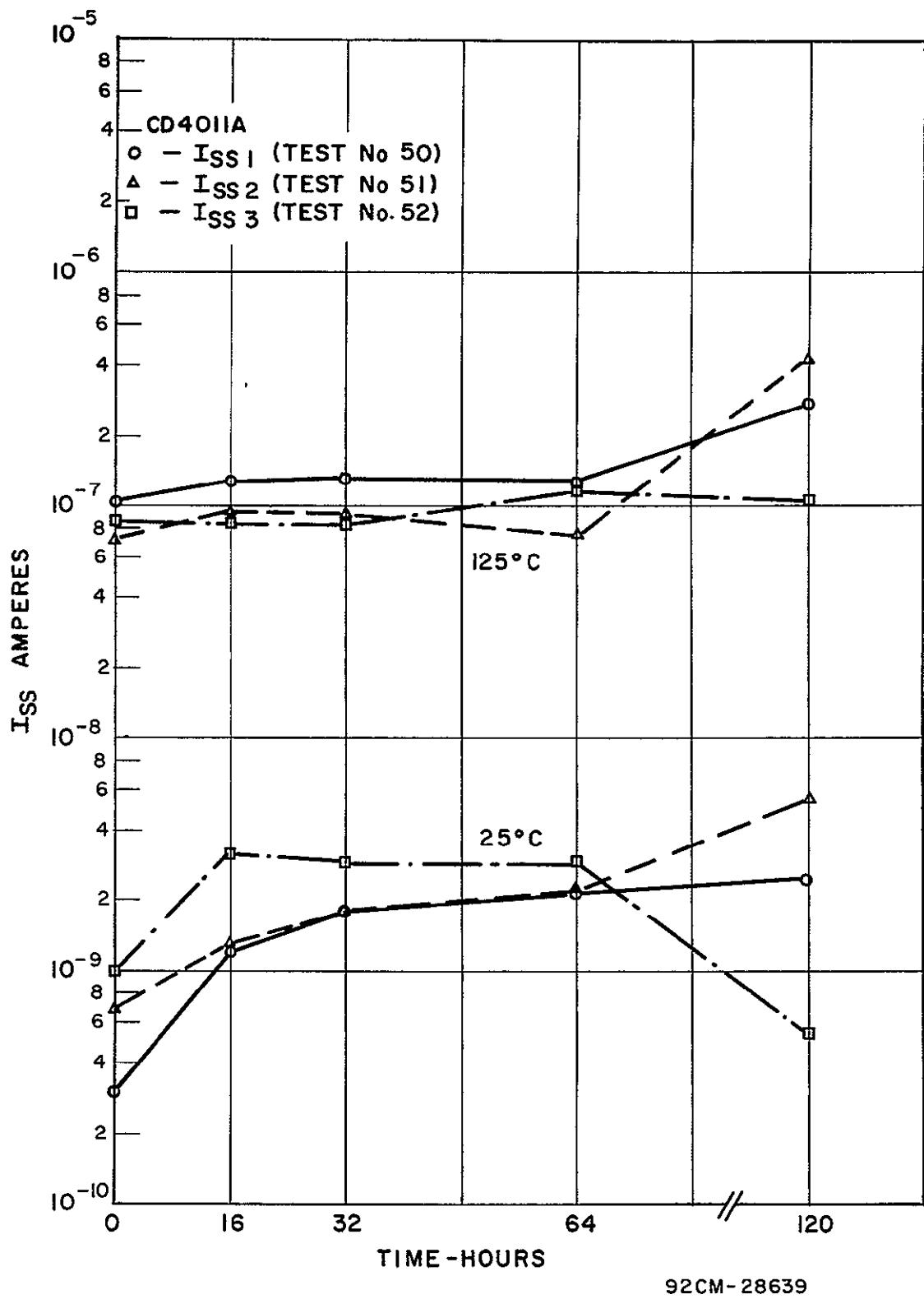
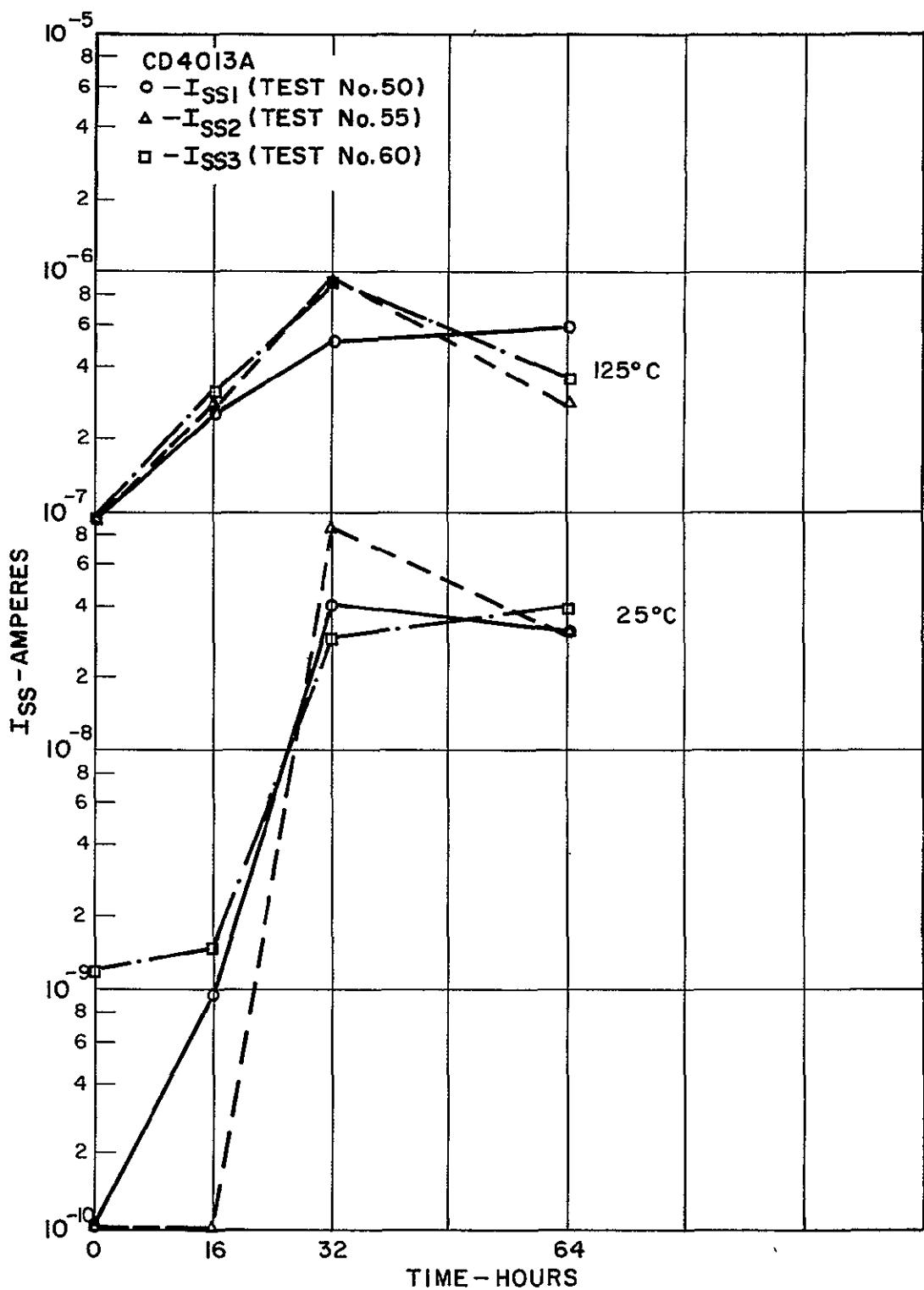


Fig. 17 - CD4011A; I_{SS} vs time; three-lot average of mean.



92CM-28641

Fig. 18 - CD4013A; I_{SS} vs time; three-lot average of mean. Only one lot was kept on life test to 64 hours. Value of $I_{SS} < 0.1$ nA are plotted on the base line.

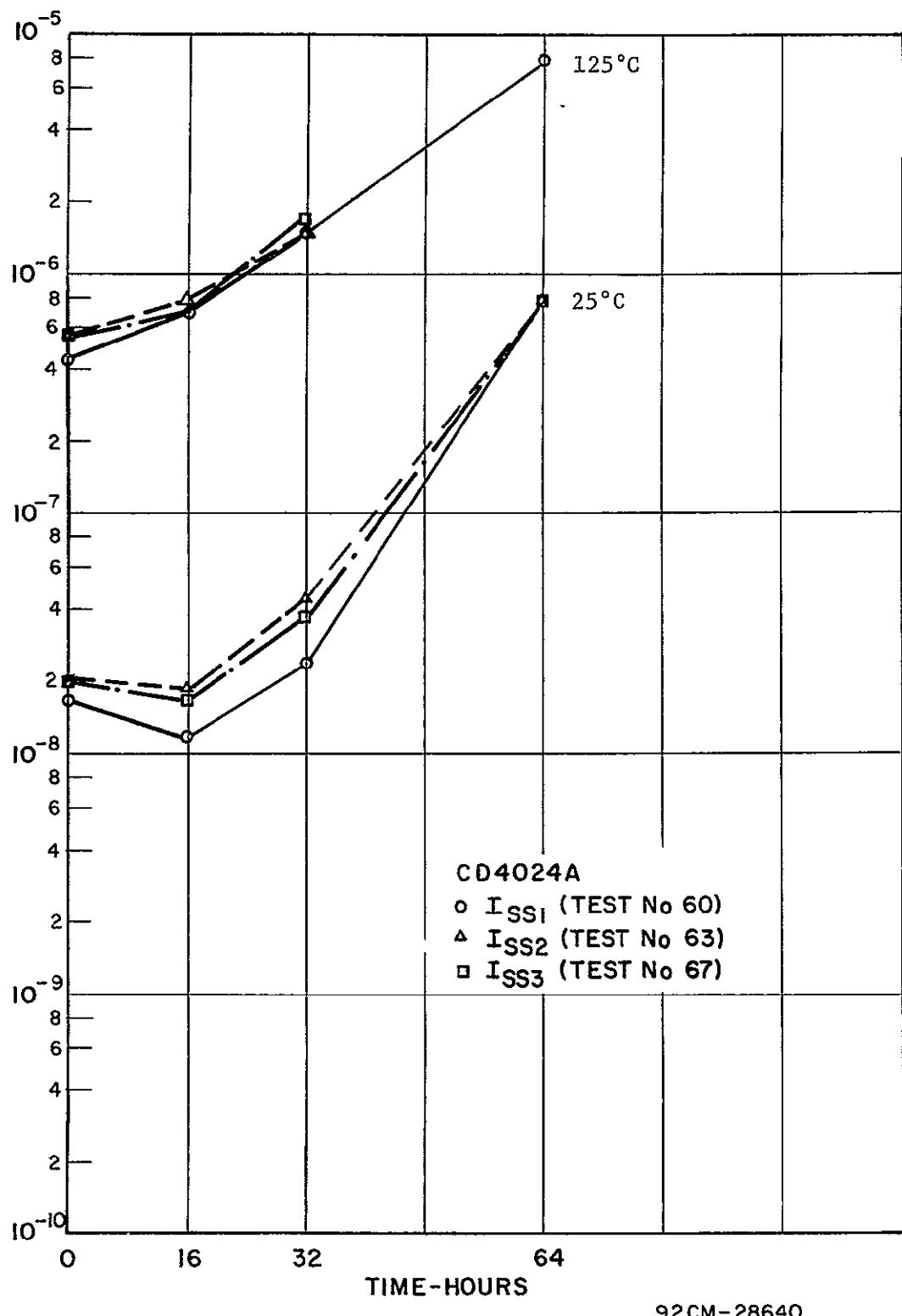


Fig. 19 - CD4024A; I_{SS} vs time; three-lot average of mean. Only one lot was kept on life test to 64 hours.

SECTION VII
PRELIMINARY FAILURE ANALYSIS

Two types of continuity failures were identified; socket problems and burned-out metallization. Test-socket problems are not considered as failures during accelerated testing.

Lot 6153060 (18/19) has failed continuity test at the 120-hour measurement point. Further tests confirmed open leads in 18 devices. External examination did not reveal lead oxidation sufficient to cause continuity problems. Consequently, two devices were opened and examined under a microscope. V_{SS} metal was found open in both devices. Fig. 20 shows photographs of one of the failed chips. No explanation for these failures will be offered at this point except to note that this type of failure is not likely to result from a gradual deterioration of the microcircuit. Further failure analysis of these devices is needed.

The predominant failure mode for all three device types is total leakage, I_{SS} and/or input leakage, I_{IL} , I_{IH} . To help determine the cause of the increase, leakage devices were baked at 200°C, no bias for 24 hours. These devices are being retested to determine whether the leakage levels have been reduced. Reduction in leakage after a high-temperature bake is generally considered as an indication of mobile ion presence.

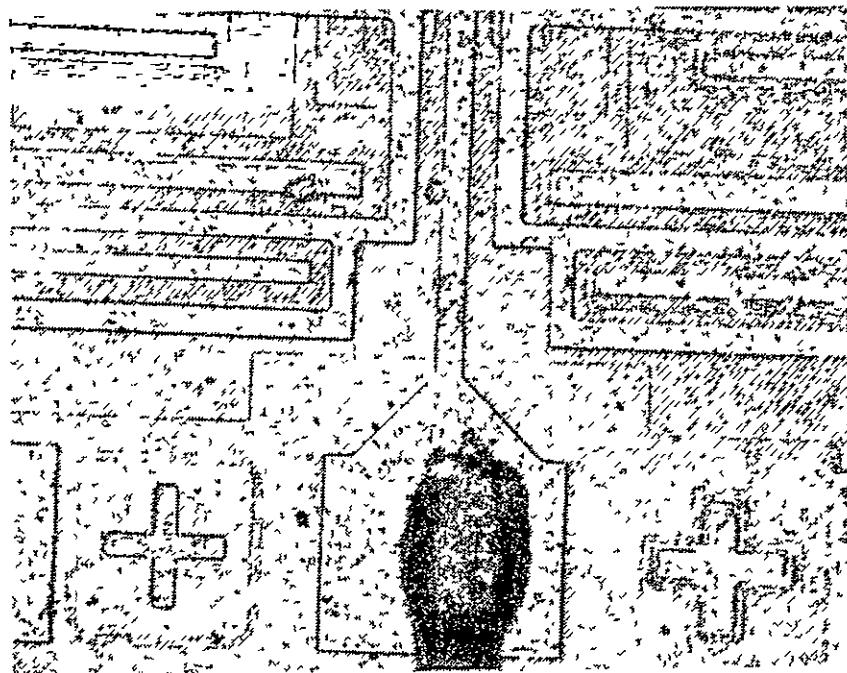
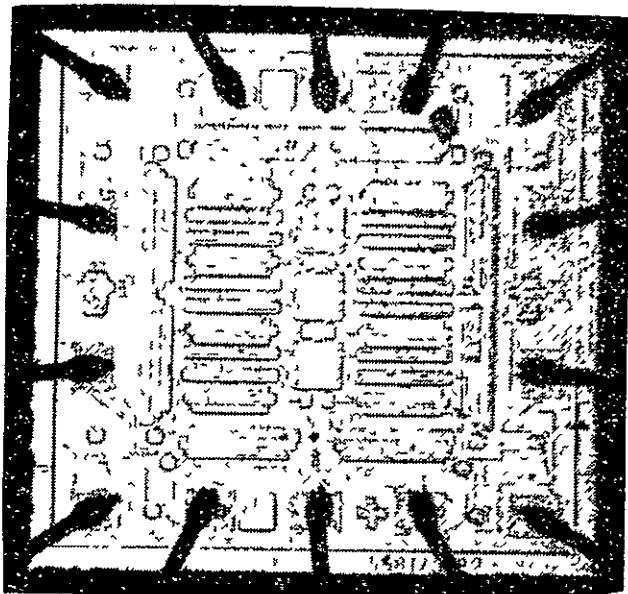


Fig. 20 - Photographs of failed CD4011 chips.

SECTION VIII

CONCLUSIONS

Recognizing that broad recommendations cannot be made until additional data is generated from Phases II and III, the following limited conclusions have been reached:

1. The three CMOS device types tested, CD4011A, CD4013A and CD4024A did not meet the requirements for Class A conformance testing delineated in MIL Std 883A Method 5005.3, Table II(a), subgroup 5; 250°C testing.
2. The utility of a 250°C accelerated life test as a predictor for CMOS long-term reliability at application temperatures has not been established.

SECTION IX
ACKNOWLEDGMENT

Acknowledgement is given Mr. E. Reiss for his guidance in this project, to Messrs. L. Campbell and F. Gusler for developing and implementing the computer test programs to Mr. H. Ahlers who had the difficult task of running an engineering program in a production environment, to Mr. C. Petrizzio and members of the Design Automation activity for their efforts in computer data analysis, and to Mr. S. Kukunaris for his help in statistical data analysis.